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Liquid-crystalline medium

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Liquid-crystalline medium

The present invention relates to a liquid-crystalline medium, to the use thereof for electro-optical purposes, and to electro-optical display devices which contain this medium.

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Liquid crystals are used principally as dielectrics in display devices, since the optical properties of such substances can be modified by an applied voltage. Electro-optical devices based on liquid crystals are extremely well known to the person skilled in the art and can be based on various effects.

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Examples of such devices are cells having dynamic scattering, DAP (deformation of aligned phases) cells, guest/host cells, TN cells having a twisted nematic structure, STN (supertwisted nematic) cells, SBE (super-birefringence effect) cells and OMI (optical mode interference) cells. The commonest display devices are based on the Schadt-Helfrich effect and

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have a twisted nematic structure.

The liquid-crystal materials must have good chemical and thermal stability and good stability to electric fields and electromagnetic radiation. Furthermore, the liquid-crystal materials should have low viscosity and produce

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short addressing times, low threshold voltages and high contrast in the cells.

They should furthermore have a suitable mesophase, for example a nematic or cholesteric mesophase for the above-mentioned cells, at the

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usual operating temperatures, i.e. in the broadest possible range above and below room temperature. Since liquid crystals are generally used as mixtures of a plurality of components, it is important that the components are readily miscible with one another. Further properties, such as the electrical conductivity, the dielectric anisotropy and the optical anisotropy,

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have to satisfy various requirements depending on the cell type and area of application. For example, materials for cells having a twisted nematic structure should have positive dielectric anisotropy and low electrical conductivity.

For example, for matrix liquid-crystal displays with integrated non-linear elements for switching individual pixels (MLC displays), media having large positive dielectric anisotropy, broad nematic phases, relatively low birefringence, very high specific resistance, good UV and temperature stability and low vapour pressure are desired.

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Matrix liquid-crystal displays of this type are known. Non-linear elements which can be used for individual switching of the individual pixels are, for example, active elements (i.e. transistors). The term "active matrix" is then used, where a distinction is made between two types:

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1. MOS (metal oxide semiconductor) or other diodes on a silicon wafer as substrate.
2. Thin-film transistors (TFTs) on a glass plate as substrate.

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The use of single-crystal silicon as substrate material restricts the display size, since even modular assembly of various part-displays results in problems at the joints.

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In the case of the more promising type 2, which is preferred, the electro-optical effect used is usually the TN effect. A distinction is made between two technologies: TFTs comprising compound semiconductors, such as, for example, CdSe, or TFTs based on polycrystalline or amorphous silicon. Intensive work is being carried out worldwide on the latter technology.

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The TFT matrix is applied to the inside of one glass plate of the display, while the other glass plate carries the transparent counterelectrode on its inside. Compared with the size of the pixel electrode, the TFT is very small and has virtually no adverse effect on the image. This technology can also be extended to fully colour-capable displays, in which a mosaic of red, green and blue filters is arranged in such a way that a filter element is opposite each switchable pixel.

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The TFT displays usually operate as TN cells with crossed polarisers in transmission and are back-lit.

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The term MLC displays here covers any matrix display with integrated non-linear elements, i.e., besides the active matrix, also displays with passive elements, such as varistors or diodes (MIM = metal-insulator-metal).

- 5 MLC displays of this type are particularly suitable for TV applications (for example pocket TVs) and for high-information displays for computer applications (for example laptops) and in automobile and aircraft construction. Besides problems regarding the angle dependence of the contrast and the response times, difficulties also arise in MLC displays due to insufficiently
10 high specific resistance of the liquid-crystal mixtures [TOGASHI, S., SEKIGUCHI, K., TANABE, H., YAMAMOTO, E., SORIMACHI, K., TAJIMA, E., WATANABE, H., SHIMIZU, H., Proc. Eurodisplay 84, Sept. 1984: A 210-288 Matrix LCD Controlled by Double Stage Diode Rings, p. 141 ff, Paris; STROMER, M., Proc. Eurodisplay 84, Sept. 1984: Design
15 of Thin Film Transistors for Matrix Addressing of Television Liquid Crystal Displays, p. 145 ff, Paris]. With decreasing resistance, the contrast of an MLC display deteriorates, and the problem of after-image elimination may occur. Since the specific resistance of the liquid-crystal mixture generally drops over the life of an MLC display owing to interaction with the interior
20 surfaces of the display, a high (initial) resistance is very important in order to achieve acceptable service lives. In particular in the case of low-volt mixtures, it was hitherto impossible to achieve very high specific resistance values. It is furthermore important that the specific resistance exhibits the smallest possible increase with increasing temperature and after heating
25 and/or UV exposure. The low-temperature properties of the mixtures from the prior art are also particularly disadvantageous. It is demanded that no crystallisation and/or smectic phases occur, even at low temperatures, and the temperature dependence of the viscosity is as low as possible. The known MLC displays do not meet these requirements.
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35 There thus continues to be a great demand for MLC displays having very high specific resistance at the same time as a large working-temperature range, short response times even at low temperatures and low threshold voltage which do not have the said disadvantages, or only do so to a reduced extent.

In addition to liquid-crystal displays which use backlighting, i.e. are operated transmissively and if desired transflectively, reflective liquid-crystal displays are also particularly interesting. These reflective liquid-crystal displays use the ambient light for information display. They thus consume
5 significantly less energy than back-lit liquid-crystal displays having a corresponding size and resolution. Since the TN effect is characterised by very good contrast, reflective displays of this type can even be read well in bright ambient conditions. This is already known of simple reflective TN displays, as used, for example, in watches and pocket calculators. However,
10 however, the principle can also be applied to high-quality, higher-resolution active matrix-addressed displays, such as, for example, TFT displays. Here, as already in the transmissive TFT-TN displays which are generally conventional, the use of liquid crystals of low birefringence (Δn) is necessary in order to achieve low optical retardation ($d \cdot \Delta n$). This low optical
15 retardation results in usually acceptable low viewing-angle dependence of the contrast (cf. German Patent 30 22 818). In reflective displays, the use of liquid crystals of low birefringence is even more important than in transmissive displays since the effective layer thickness through which the light passes is approximately twice as large in reflective displays as in transmissive displays having the same layer thickness.
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The advantages of reflective displays over transmissive displays, besides the lower power consumption (since backlighting is unnecessary), are the space saving, which results in a very small physical depth, and the reduction in problems due to temperature gradients caused by different degrees
25 of heating by the backlighting.

In TN (Schadt-Helfrich) cells, media are desired which facilitate the following advantages in the cells:
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- extended nematic phase range (in particular at low temperatures),
- the ability to switch at extremely low temperatures (outdoor use, automobiles, avionics),

- elevated resistance against UV radiation (longer life),
- low rotational viscosities,
- low threshold (addressing) voltage and
- high birefringence for thinner layer thicknesses and thus shorter response times.

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The media available from the prior art do not allow these advantages to be
10 achieved while simultaneously retaining the other parameters.

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In the case of supertwisted (STN) cells, media are desired which enable greater multiplexability and/or lower threshold voltages and/or broader nematic phase ranges (in particular at low temperatures). To this end, a further widening of the available parameter latitude (clearing point, smectic-nematic transition or melting point, viscosity, dielectric parameters, elastic parameters) is urgently desired.

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In addition, the trend in monitor and TV applications is towards ever-shorter response times. The display manufacturers are reducing the response time through the use of displays of smaller layer thickness. At constant optical path length $d \cdot \Delta n$, this requires liquid-crystal mixtures of greater Δn . In addition, the use of liquid-crystal mixtures of low rotational viscosity likewise results in a shortening of the response times.

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The present invention thus had the object of providing media for MLC, TN or STN displays of this type, preferably for MLC and TN displays and particularly preferably for transmissive TN displays, which do not have the above-mentioned disadvantages or only do so to a reduced extent, and at the same time preferably have very low rotational viscosities γ_1 and relatively high optical anisotropy values Δn . The mixtures according to the invention should preferably find use in transmissive applications.

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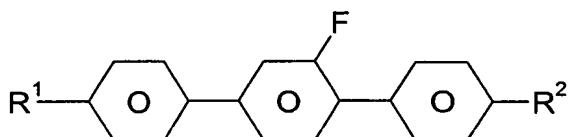
It has now been found that these objects can be achieved if the media according to the invention are used in displays.

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The present invention thus relates to a liquid-crystalline medium based on a mixture of polar compounds of positive or negative dielectric anisotropy which is characterised in that it comprises one or more compounds of the general formula I

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in which

R¹ and R² are each, independently of one another, identically or differently, H, an alkyl radical having from 1 to 12 carbon atoms which is unsubstituted, monosubstituted by CN or CF₃ or at least monosubstituted by halogen, where, in addition, one or more CH₂ groups in these radicals may each, independently of one another, be replaced by -O-, -S-, ——, -CH=CH-, -C≡C-, -CO-, -CO-O-, -O-CO- or -O-CO-O- in such a way that O atoms are not linked directly to one another.

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The compounds of the formula I have a broad range of applications. These compounds can either serve as base materials of which liquid-crystalline media are predominantly composed, or they can be added to liquid-crystalline base materials from other classes of compound in order, for example, to modify the dielectric and/or optical anisotropy of a dielectric of this type and/or to optimise its threshold voltage and/or its viscosity.

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In the pure state, the compounds of the formula I are colourless and form liquid-crystalline mesophases in a temperature range which is favourably located for electro-optical use. They are stable chemically, thermally and to light.

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If R¹ and/or R² are an alkyl radical, this may be straight-chain or branched. It is preferably straight-chain, has 1, 2, 3, 4, 5, 6, 7, 8 or 9 carbon atoms and accordingly is preferably methyl, ethyl, propyl, butyl, pentyl, hexyl, heptyl, octyl or nonyl, furthermore decyl, undecyl or dodecyl. Groups having from 1 to 5 carbon atoms are particularly preferred.

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If R¹ and/or R² are an alkoxy radical, this may be straight-chain or branched. It is preferably straight-chain, has 1, 2, 3, 4, 5, 6, 7, 8 or 9 carbon atoms and accordingly is preferably methoxy, ethoxy, propoxy, butoxy, pentoxy, hexoxy, heptoxy, octoxy or nonoxy, furthermore decoxy or 10 undecoxy.

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If R¹ and/or R² are an oxaalkyl radical, this may be straight-chain or branched. It is preferably straight-chain, has 1, 2, 3, 4, 5, 6, 7, 8 or 15 9 carbon atoms and accordingly is preferably 2-oxapropyl (= methoxy-methyl), 2- (= ethoxymethyl) or 3-oxabutyl (= 2-methoxyethyl), 2-, 3- or 4-oxapentyl, 2-, 3-, 4- or 5-oxahexyl, 2-, 3-, 4-, 5- or 6-oxaheptyl, 2-, 3-, 4-, 5-, 6- or 7-oxaoctyl, 2-, 3-, 4-, 5-, 6-, 7- or 8-oxanonyl or 2-, 3-, 4-, 5-, 6-, 7-, 8- or 9-oxadecyl.

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If R¹ and/or R² are an alkyl radical in which one CH₂ group has been replaced by -CH=CH-, this may be straight-chain or branched. It is preferably straight-chain and has from 2 to 10 carbon atoms. Accordingly, it is particularly preferably vinyl, prop-1- or -2-enyl, but-1-, -2- or -3-enyl, pent-1-, -2-, -3- or -4-enyl, hex-1-, -2-, -3-, -4- or -5-enyl, hept-1-, -2-, -3-, 25 -4-, -5- or -6-enyl, oct-1-, -2-, -3-, -4-, -5-, -6- or -7-enyl, non-1-, -2-, -3-, -4-, -5-, -6-, -7- or -8-enyl, or dec-1-, -2-, -3-, -4-, -5-, -6-, -7-, -8- or -9-enyl.

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If R¹ and/or R² are an alkyl radical in which one CH₂ group has been replaced by -O- and one has been replaced by -CO-, these are preferably 30 adjacent. These thus contain an acyloxy group -CO-O- or an oxycarbonyl group -O-CO-. These are preferably straight-chain and have from 2 to 6 carbon atoms. Accordingly, they are particularly preferably acetoxy, propionyloxy, butyryloxy, pentanoyloxy, hexanoyloxy, acetoxyethyl, propionyloxymethyl, butyryloxymethyl, pentanoyloxymethyl, 2-acetoxyethyl, 35 2-propionyloxethyl, 2-butyryloxyethyl, 3-acetoxypropyl,

3-propionyloxypropyl, 4-acetoxybutyl, methoxycarbonyl, ethoxycarbonyl, propoxycarbonyl, butoxycarbonyl, pentoxy carbonyl, methoxycarbonylmethyl, ethoxycarbonylmethyl, propoxycarbonylmethyl, butoxycarbonylmethyl, 2-(methoxycarbonyl)ethyl, 2-(ethoxycarbonyl)ethyl, 2-(propoxy carbonyl)ethyl, 3-(methoxycarbonyl)propyl, 3-(ethoxycarbonyl)propyl or 4-(methoxycarbonyl)butyl.

If R¹ and/or R² are an alkyl radical in which one CH₂ group has been replaced by unsubstituted or substituted -CH=CH- and an adjacent CH₂ group has been replaced by -CO-, -CO-O- or -O-CO-, this may be straight-chain or branched. It is preferably straight-chain and has from 4 to 12 carbon atoms. Accordingly, it is particularly preferably acryloyloxymethyl, 2-acryloyloxyethyl, 3-acryloyloxypropyl, 4-acryloyloxybutyl, 5-acryloyloxy-pentyl, 6-acryloyloxyhexyl, 7-acryloyloxyheptyl, 8-acryloyloxyoctyl, 9-acryloyloxy nonyl, 10-acryloyloxydecyl, methacryloyloxymethyl, 2-methacryloyloxyethyl, 3-methacryloyloxypropyl, 4-methacryloyloxybutyl, 5-methacryloyloxy pentyl, 6-methacryloyloxyhexyl, 7-methacryloyloxyheptyl, 8-methacryloyloxyoctyl or 9-methacryloyloxy nonyl.

If R¹ and/or R² are an alkyl or alkenyl radical which is monosubstituted by CN or CF₃, this radical is preferably straight-chain. The substitution by CN or CF₃ is possible in any desired position.

If R¹ and/or R² are an alkyl or alkenyl radical which is at least monosubstituted by halogen, this radical is preferably straight-chain and halogen is preferably F or Cl. In the case of polysubstitution, halogen is preferably F. The resultant radicals also include perfluorinated radicals. In the case of monosubstitution, the fluorine or chlorine substituent can be in any desired position, but preferably in the ω -position.

Compounds of the formula I which contain wing groups R¹ and/or R² which are suitable for polymerisation reactions are suitable for the preparation of liquid-crystalline polymers.

Compounds of the formula I containing branched wing groups R¹ and/or R² may occasionally be of importance owing to better solubility in the

conventional liquid-crystalline base materials, but in particular as chiral dopants if they are optically active. Smectic compounds of this type are suitable as components of ferroelectric materials.

Compounds of the formula I having S_A phases are suitable, for example,

5 for thermally addressed displays.

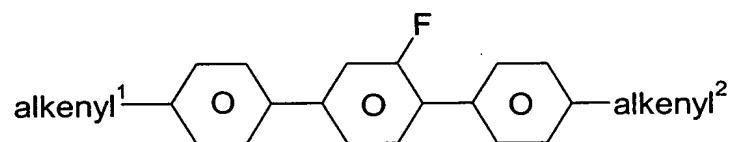
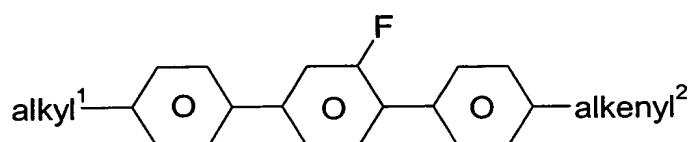
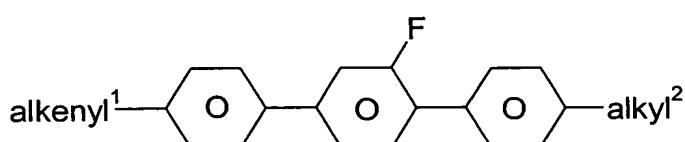
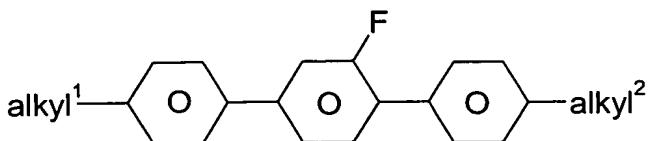
Branched groups of this type preferably contain not more than one chain branch. Preferred branched radicals R¹ and/or R² are isopropyl, 2-butyl (= 1-methylpropyl), isobutyl (= 2-methylpropyl), 2-methylbutyl, isopentyl (= 3-methylbutyl), 2-methylpentyl, 3-methylpentyl, 2-ethylhexyl, 2-propylpentyl, isopropoxy, 2-methylpropoxy, 2-methylbutoxy, 3-methylbutoxy, 2-methylpentoxy, 3-methylpentoxy, 2-ethylhexoxy, 1-methylhexoxy and 1-methylheptoxy.

15 If R¹ and/or R² are an alkyl radical in which two or more CH₂ groups have been replaced by -O- and/or -CO-O-, this may be straight-chain or branched. It is preferably branched and has from 3 to 12 carbon atoms. Accordingly, it is particularly preferably biscarboxymethyl, 2,2-biscarboxyethyl, 3,3-biscarboxypropyl, 4,4-biscarboxybutyl, 5,5-biscarboxypentyl, 20 6,6-biscarboxyhexyl, 7,7-biscarboxyheptyl, 8,8-biscarboxyoctyl, 9,9-bis-carboxynonyl, 10,10-biscarboxydecyl, bis(methoxycarbonyl)methyl, 2,2-bis-(methoxycarbonyl)ethyl, 3,3-bis(methoxycarbonyl)propyl, 4,4-bis(methoxy-carbonyl)butyl, 5,5-bis(methoxycarbonyl)pentyl, 6,6-bis(methoxy-carbonyl)hexyl, 7,7-bis(methoxycarbonyl)heptyl, 8,8-bis(methoxycarbonyl)-octyl, bis(ethoxycarbonyl)methyl, 2,2-bis(ethoxycarbonyl)ethyl, 3,3-bis-(ethoxycarbonyl)propyl, 4,4-bis(ethoxycarbonyl)butyl or 5,5-bis(ethoxy-carbonyl)pentyl.

25 R¹ and/or R² are preferably, independently of one another, identically or differently, H, a straight-chain alkyl radical having from 1 to 9 carbon atoms or a straight-chain alkenyl radical having from 2 to 9 carbon atoms.

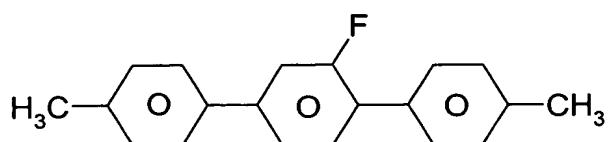
The compounds of the formula I are consequently preferably selected from the group consisting of the compounds of the following sub-formulae Ia to Id, where sub-formula Ia is particularly preferred:

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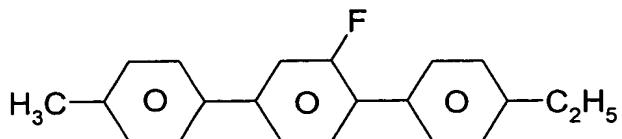


where, in the formulae Ia to Id, the term "alkyl¹" and "alkyl²" in each case, independently of one another, identically or differently, denotes a hydrogen atom or an alkyl radical having from 1 to 9 carbon atoms, preferably a straight-chain alkyl radical having from 1 to 5 carbon atoms, and the term "alkenyl¹" and "alkenyl²" in each case, independently of one another, identically or differently, denotes an alkenyl radical having from 2 to 9 carbon atoms, preferably a straight-chain alkenyl radical having from 2 to 5 carbon atoms.

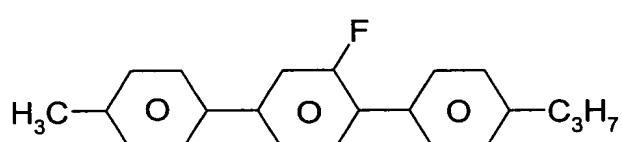
The compounds of the formula I are consequently particularly preferably selected from the group consisting of the compounds of the following sub-formulae I1 to I25:



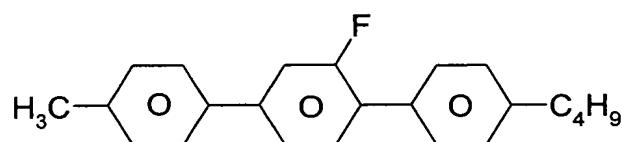
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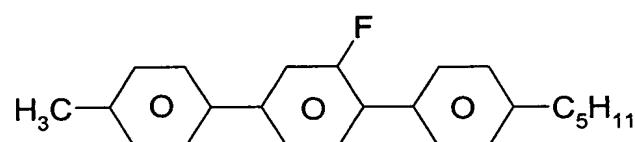
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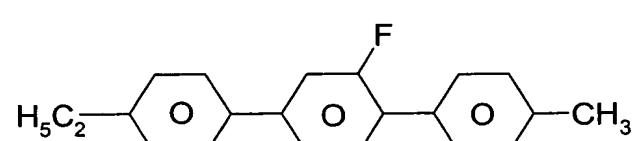
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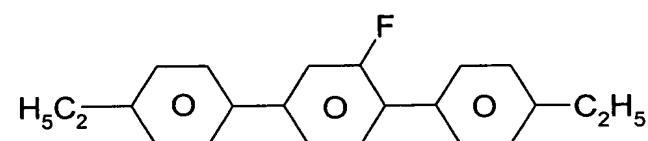
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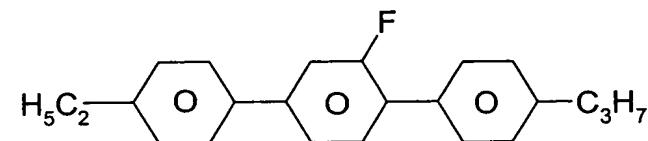
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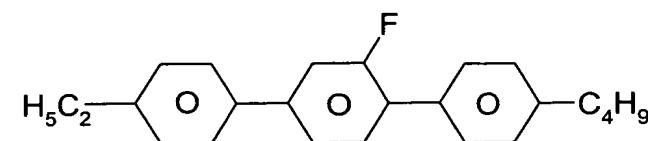
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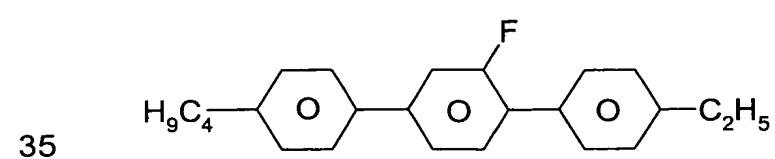
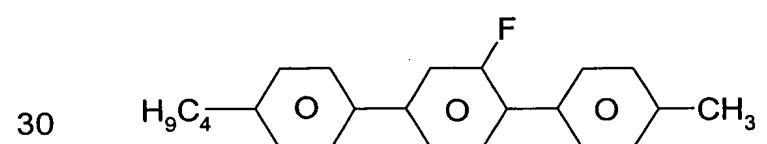
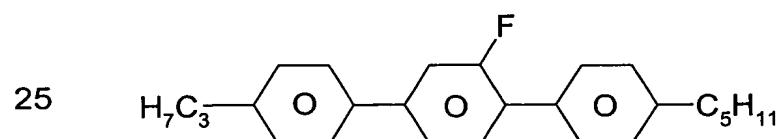
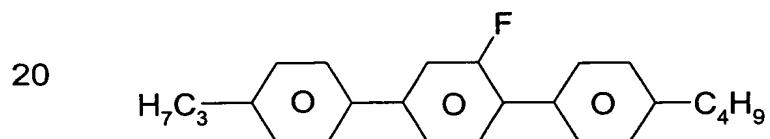
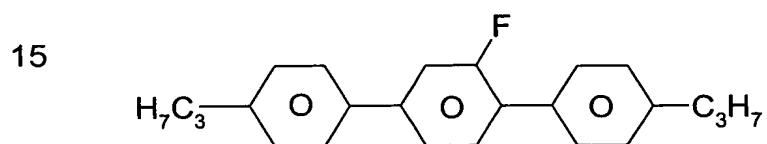
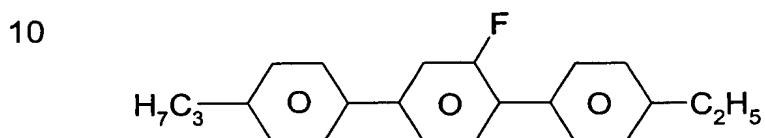
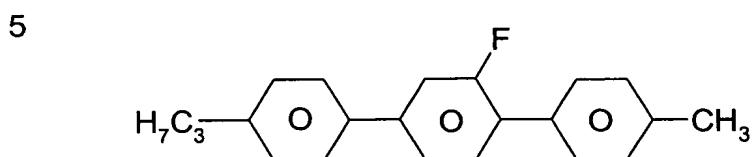
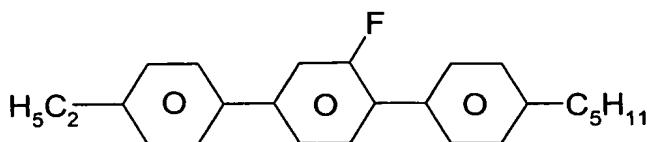
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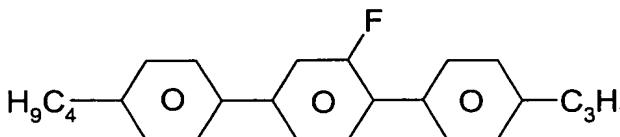
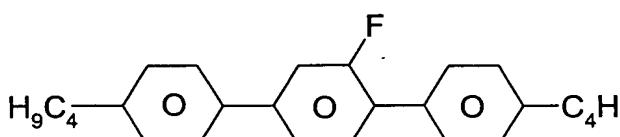
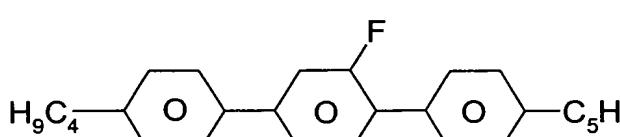
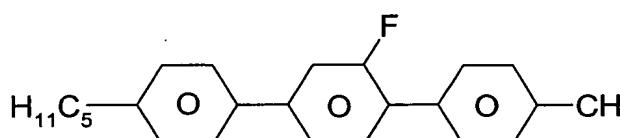
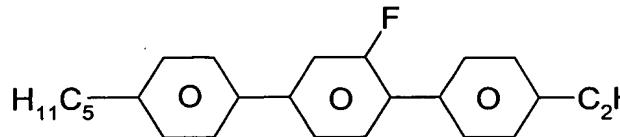
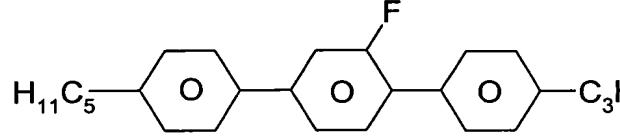
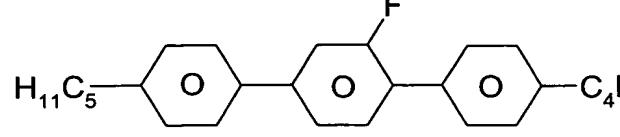
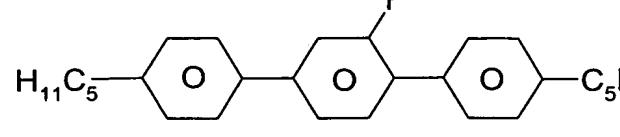


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- 18  I18
- 5  I19
- 10  I20
- 15  I21
- 20  I22
- 25  I23
- 30  I24
- 35  I25

Particularly preferred compounds from the group consisting of the compounds of the sub-formulae I1 to I25 here are compounds in which the total number of carbon atoms in the two alkyl groups is in the range from 4 to 6. These are the compounds I3 to I5, I7 to I9, I11 to I13, I16, I17 and I21. Particular preference is given here to the sub-formulae I8, I9, I12 and I13.

The liquid-crystalline medium particularly preferably comprises one, two or three compounds of the formula I.

10 The proportion of compounds of the formula I in the mixture as a whole is from 1 to 60% by weight, preferably from 3 to 50% by weight and particularly preferably either from 3 to 12% by weight (embodiment A) or from 15 to 50% by weight (embodiment B).

15 The compounds of the formula I are prepared by methods known per se, as described in the literature (for example in the standard works, such as Houben-Weyl, Methoden der organischen Chemie [Methods of Organic Chemistry], Georg-Thieme-Verlag, Stuttgart), to be precise under reaction 20 conditions which are known and suitable for the said reactions. Use can also be made here of variants which are known per se, but are not mentioned here in greater detail.

25 The compounds of the formula I are preferably prepared as described in EP 0 132 377 A2.

The present invention also relates to electro-optical display devices (in particular STN or MLC displays having two plane-parallel outer plates, which, together with a frame, form a cell, integrated non-linear elements 30 for switching individual pixels on the outer plates, and a nematic liquid-crystal mixture of positive dielectric anisotropy and high specific resistance which is located in the cell) which contain the media according to the invention, and to the use of these media for electro-optical purposes. Besides reflective applications, the mixtures according to the invention are

- 15 -

also suitable for IPS (in plane switching) applications and OCB (optically controlled birefringence) applications.

The liquid-crystal mixtures according to the invention enable a significant widening of the available parameter latitude.

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The achievable combinations of rotational viscosity γ_1 and optical anisotropy Δn are far superior to previous materials from the prior art.

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The requirement for a high clearing point, nematic phase at low temperature, low rotational viscosity γ_1 and high Δn has hitherto only been achieved to an inadequate extent. Although systems such as, for example, the mixture of Comparative Example 2, which is commercially available from Merck, have similar properties to the mixtures according to the invention, they have, however, significantly worse values for the rotational viscosity γ_1 .

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Other mixture systems, such as, for example, the mixture of Comparative Example 1, which is commercially available from Merck, have comparable rotational viscosities γ_1 , but have significantly worse values for the optical anisotropy Δn .

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The liquid-crystal mixtures according to the invention, while retaining the nematic phase down to -20°C, preferably down to -30°C and particularly preferably down to -40°C, enable clearing points above 65°C, preferably above 70°C and particularly preferably above 75°C, simultaneously dielectric anisotropy values $\Delta \epsilon$ of ≥ 4 , preferably ≥ 4.5 , and a high value for the specific resistance to be achieved, enabling excellent STN and MLC displays to be obtained. In particular, the mixtures are characterised by low operating voltages. The TN thresholds are below 2.0 V, preferably below 1.9 V and particularly preferably below 1.8 V.

The liquid-crystal mixtures according to the invention have optical anisotropies Δn which, in the case of embodiment A, are preferably ≤ 0.100 and particularly preferably ≤ 0.095 . In the case of embodiment B,

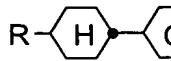
the optical anisotropies are preferably ≥ 0.160 , particularly preferably ≥ 0.180 and in particular ≥ 0.200 .

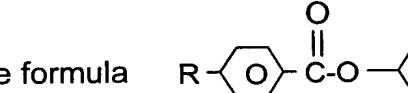
It goes without saying that, through a suitable choice of the components of the mixtures according to the invention, it is also possible for higher clearing points to be achieved at higher threshold voltages or lower clearing points to be achieved at lower threshold voltages with retention of the other advantageous properties. At viscosities correspondingly increased only slightly, it is likewise possible to obtain mixtures having greater $\Delta\epsilon$ and thus lower thresholds. The MLC displays according to the invention preferably operate at the first Gooch and Tarry transmission minimum [C.H. Gooch and H.A. Tarry, Electron. Lett. 10, 2-4, 1974; C.H. Gooch and H.A. Tarry, Appl. Phys., Vol. 8, 1575-1584, 1975], where particularly favourable electro-optical properties, such as, for example, high steepness of the characteristic line and low angle dependence of the contrast (German Patent 30 22 818), are achieved. In addition, significantly higher specific resistances can be achieved using the mixtures according to the invention at the first minimum than in the case of mixtures comprising cyano compounds. Through a suitable choice of the individual components and their proportions by weight, the person skilled in the art is able to set the birefringence necessary for a pre-specified layer thickness of the MLC display using simple routine methods.

The rotational viscosity γ_1 of the mixtures according to the invention at 20°C is preferably $\leq 180 \text{ mPa}\cdot\text{s}$, particularly preferably $\leq 160 \text{ mPa}\cdot\text{s}$. In a specific embodiment (embodiment A), the rotational viscosity γ_1 is particularly preferably $\leq 80 \text{ mPa}\cdot\text{s}$ and in particular $\leq 70 \text{ mPa}\cdot\text{s}$. The ratio γ_1 to $(\Delta n)^2$ here is preferably ≤ 8000 , particularly preferably ≤ 7000 . In a specific embodiment (embodiment B), the ratio is particularly preferably ≤ 5000 and in particular ≤ 4500 . The nematic phase range is preferably at least 90°C and extends at least from -20° to +70°C.

Measurements of the capacity holding ratio (HR) [S. Matsumoto et al., Liquid Crystals 5, 1320 (1989); K. Niwa et al., Proc. SID Conference, San Francisco, June 1984, p. 304 (1984); G. Weber et al., Liquid Crystals 5, 1381 (1989)] have shown that mixtures according to the invention com-

prising compounds of the formula I exhibit a significantly smaller decrease in the HR with increasing temperature than analogous mixtures comprising

cyanophenylcyclohexanes of the formula  or esters of

5 the formula  instead of the compounds of the formula I according to the invention.

The UV stability of the mixtures according to the invention is also considerably better, i.e. they exhibit a significantly smaller decrease in the HR on 10 exposure to UV.

Besides at least one compound of the formula I, the medium according to the invention additionally comprises one or more compounds selected from the group consisting of compounds of the general formulae II to X:

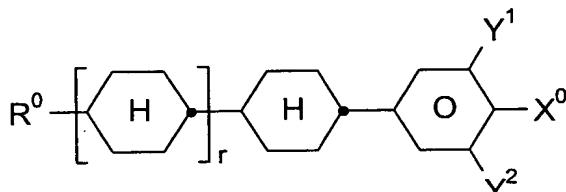
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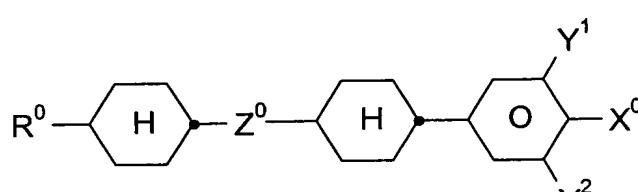
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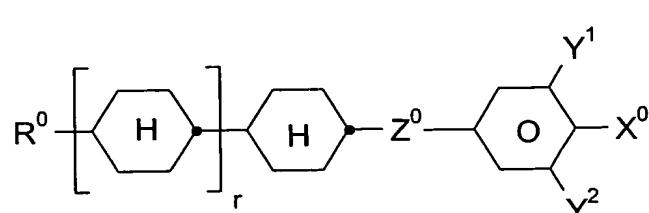
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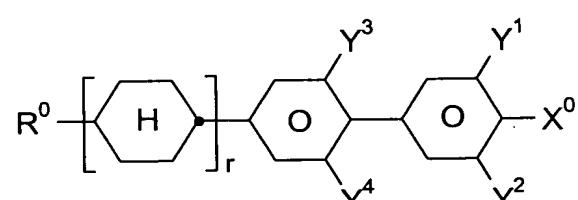
II



III

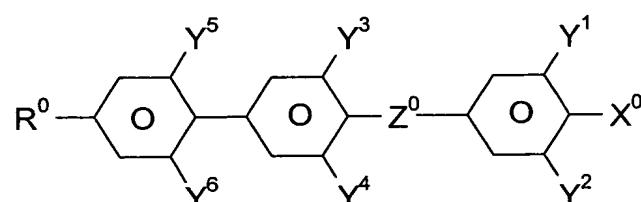
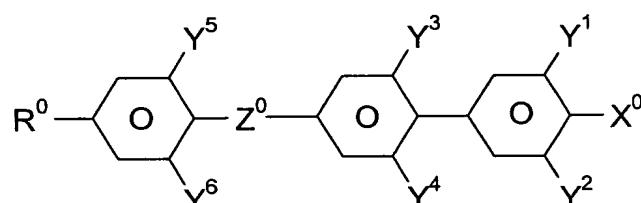
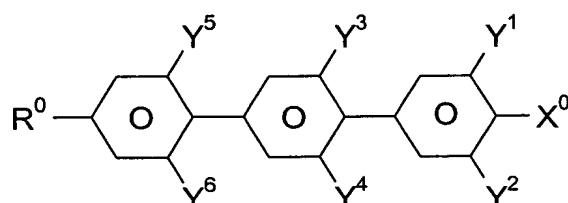
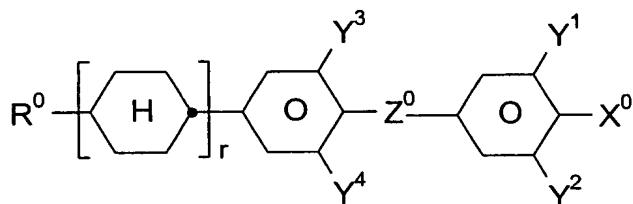
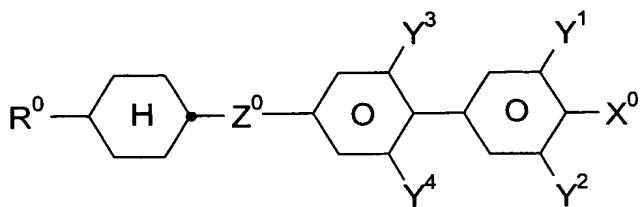


IV



V

- 18 -



in which the individual radicals have the following meanings:

30 R^0 : n-alkyl, oxaalkyl, fluoroalkyl or alkenyl, each having up to
9 carbon atoms;

X^0 : F, Cl, halogenated alkyl or halogenated alkoxy having from
1 to 6 carbon atoms, or halogenated alkenyl having from 2 to
6 carbon atoms;

- 19 -

Z⁰: -CF₂O-, -OCF₂-, -CH₂O-, -OCH₂-, -CO-O-, -O-CO-, -CH=CH-, -C₂H₄-, -C₂F₄-, -CH₂CF₂-, -CF₂CH₂- or -C₄H₈;

Y¹, Y², Y³, Y⁴,

Y⁵ and Y⁶: each, independently of one another, H or F;

5

r: 0 or 1, preferably 1.

The term "alkyl" covers straight-chain and branched alkyl groups having from 1 to 9 carbon atoms, preferably the straight-chain groups methyl,

10 ethyl, propyl, butyl, pentyl, hexyl, heptyl, octyl and nonyl. Groups having from 1 to 5 carbon atoms are particularly preferred.

The term "alkenyl" covers straight-chain and branched alkenyl groups having from 2 to 9 carbon atoms, preferably the straight-chain groups

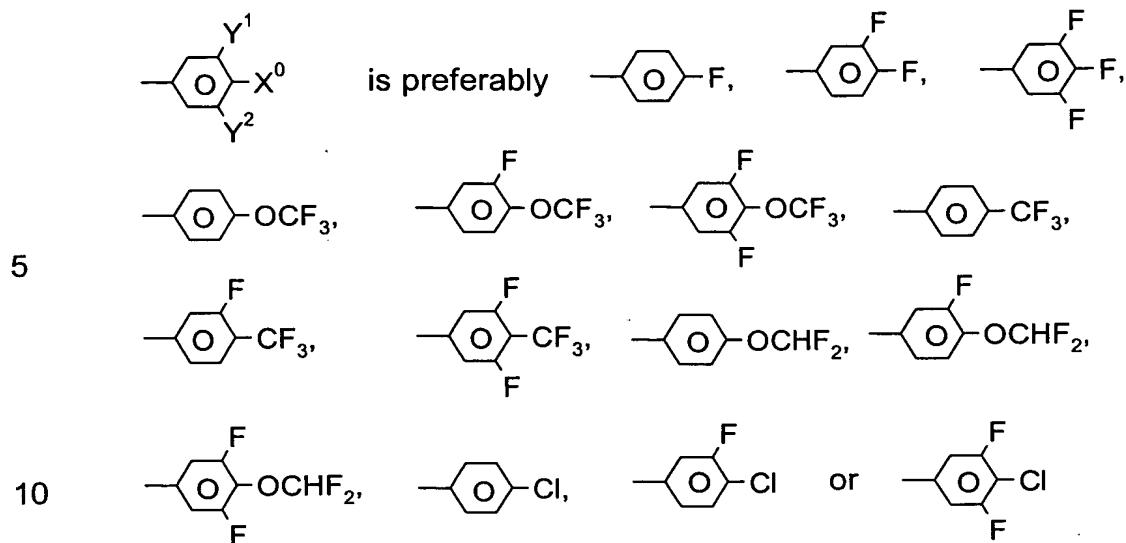
15 having from 2 to 7 carbon atoms. Preferred alkenyl groups are C₂-C₇-1E-alkenyl, C₄-C₇-3E-alkenyl, C₅-C₇-4-alkenyl, C₆-C₇-5-alkenyl and C₇-6-alkenyl, in particular C₂-C₇-1E-alkenyl, C₄-C₇-3E-alkenyl and C₅-C₇-4-alkenyl. Examples of preferred alkenyl groups are vinyl, 1E-propenyl, 1E-butenyl, 1E-pentenyl, 1E-hexenyl, 1E-heptenyl, 3-butenyl, 20 3E-pentenyl, 3E-hexenyl, 3E-heptenyl, 4-pentenyl, 4Z-hexenyl, 4E-hexenyl, 4Z-heptenyl, 5-hexenyl, 6-heptenyl and the like. Groups having up to 5 carbon atoms are particularly preferred.

25 The term "fluoroalkyl" preferably covers straight-chain groups having a terminal fluorine, i.e. fluoromethyl, 2-fluoroethyl, 3-fluoropropyl, 4-fluorobutyl, 5-fluoropentyl, 6-fluorohexyl and 7-fluoroheptyl. However, other positions of the fluorine are not excluded.

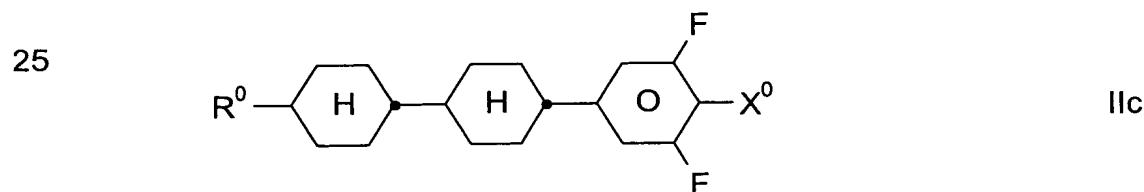
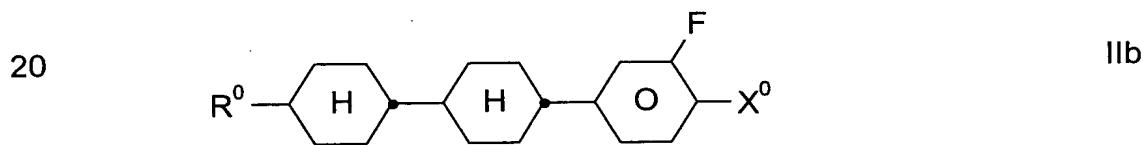
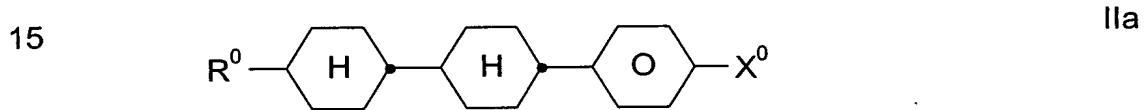
30 The term "oxaalkyl" preferably covers straight-chain radicals of the formula C_nH_{2n+1}-O-(CH₂)_m, in which n and m are each, independently of one another, from 1 to 6. Preferably, n = 1 and m = 1 to 6.

In the formulae II to X,

- 20 -



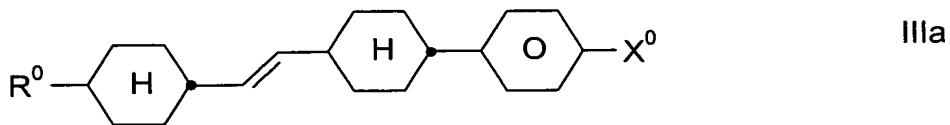
The compound of the formula II is preferably



30 in which R^0 and X^0 can adopt the meanings indicated above. Preferably, however, R^0 is n-alkyl or alkenyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms or alkenyl having from 2 to 5 carbon atoms, and X^0 is F, OCF₃, CF₃ or OCHF₂.

35 The compound of the formula III is preferably

- 21 -



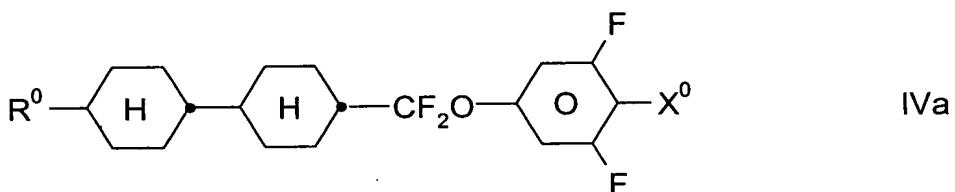
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in which R^0 and X^0 can adopt the meanings indicated above. Preferably, however, R^0 is n-alkyl or alkenyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms or alkenyl having from 2 to 5 carbon atoms, and X^0 is F, OCF_3 , CF_3 or $OCHF_2$.

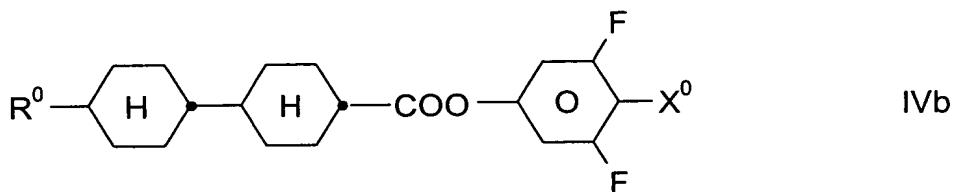
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The compound of the formula IV is preferably

15



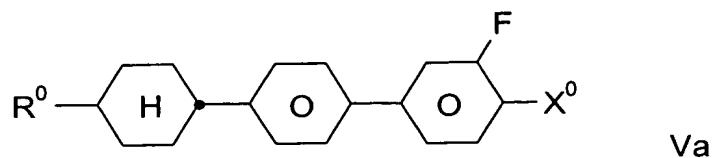
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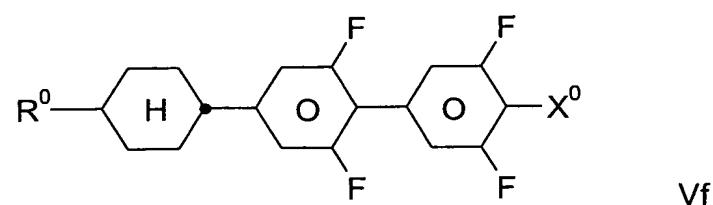
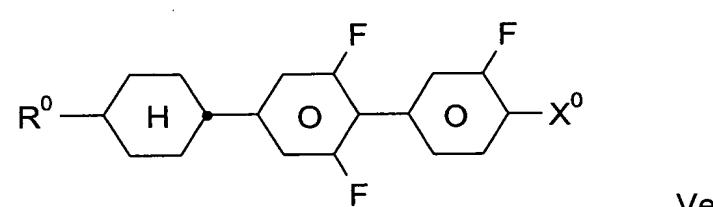
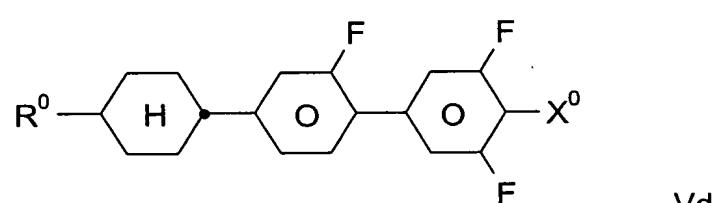
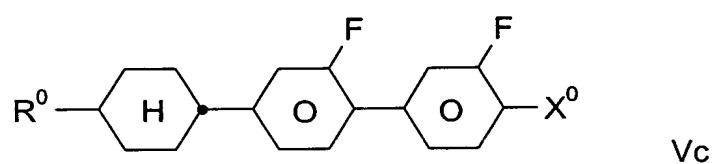
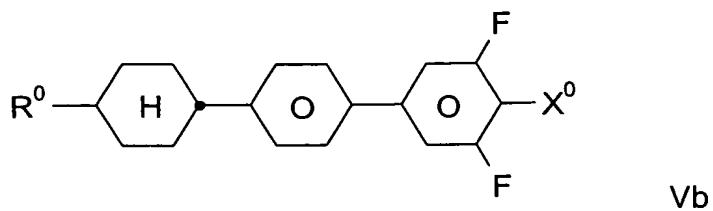
in which R^0 and X^0 can adopt the meanings indicated above. Preferably, however, R^0 is n-alkyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms, and X^0 is F, OCF_3 , CF_3 or $OCHF_2$, particularly preferably F.

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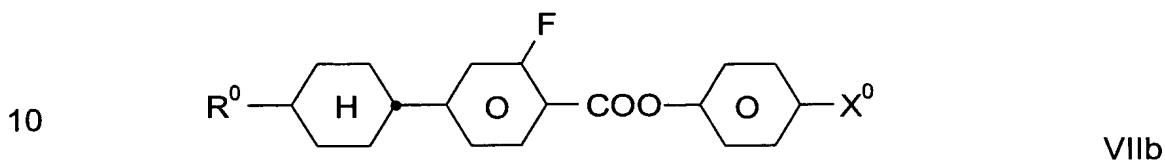
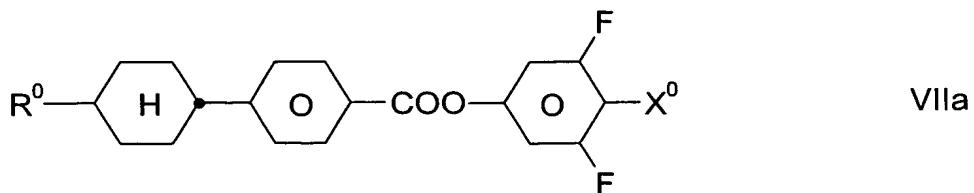
- 22 -



in which R^0 and X^0 can adopt the meanings indicated above. Preferably,
 30 however, R^0 is n-alkyl having up to 9 carbon atoms, particularly preferably
 n-alkyl having from 1 to 5 carbon atoms, and X^0 is F, OCF_3 , CF_3 or $OCHF_2$,
 particularly preferably F. Particular preference is given to the formula Vc.

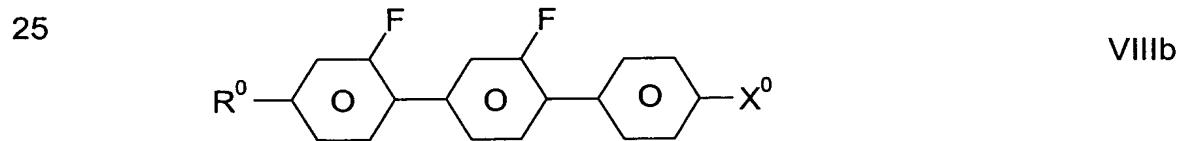
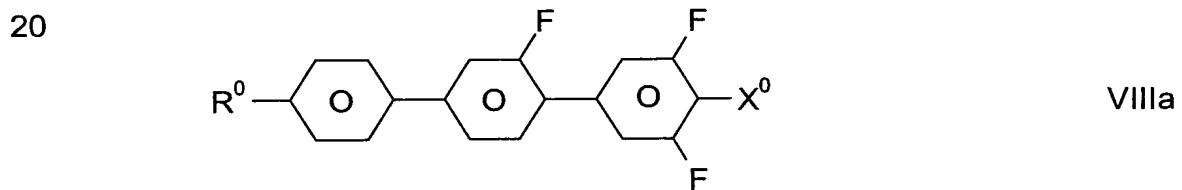
- 23 -

The compound of the formula VII is preferably



15 in which R⁰ and X⁰ can adopt the meanings indicated above. Preferably, however, R⁰ is n-alkyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms, and X⁰ is F, OCF₃, CF₃ or OCHF₂.

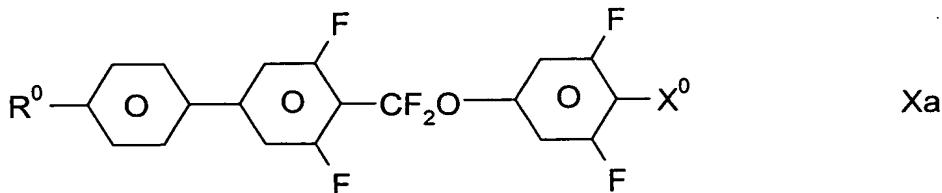
The compound of the formula VIII is preferably



30 in which R⁰ and X⁰ can adopt the meanings indicated above. Preferably, however, R⁰ is n-alkyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms, and X⁰ is F, OCF₃, CF₃ or OCHF₂, particularly preferably F.

The compound of the formula X is preferably

5



in which R^0 and X^0 can adopt the meanings indicated above. Preferably, however, R^0 is n-alkyl having up to 9 carbon atoms, particularly preferably

10 n-alkyl having from 1 to 5 carbon atoms, and X^0 is F, OCF₃, CF₃ or OCHF₂,

particularly preferably F.

Particularly preferred embodiments are indicated below.

15

- The medium comprises one or more compounds of the formulae II, III, IV, V, VI, VII, VIII, IX and/or X, preferably one or more compounds of the formulae IIa, IIb, IIc, IIIa, IVa, IVb, Vc, VIIa, VIIb, VIIla, VIIlb and/or Xa.

20

- The proportion of compounds of the formulae II to X in the mixture as a whole is from 20 to 70% by weight, preferably from 30 to 60% by weight and particularly preferably from 35 to 55% by weight.

25

- The proportion of compounds of the formulae I to X together in the mixture as a whole is at least 30% by weight, preferably at least 40% by weight and particularly preferably at least 50% by weight.

30

- The medium essentially consists of compounds of the formulae I to X.
- The I : (II + III + IV + V + VI + VII + VIII + IX + X) weight ratio is preferably in the range from 1 : 10 to 10 : 1.

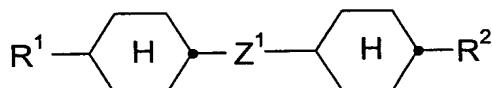
- 25 -

The optimum mixing ratio of the compounds of the formulae I and II + III + IV + V + VI + VII + VIII + IX + X depends substantially on the desired properties, on the choice of the components of the formulae I, II, III, IV, V, VI, VII, VIII, IX and/or X and on the choice of any other components present. Suitable mixing ratios within the ranges indicated above can

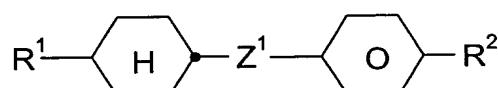
5 easily be determined from case to case.

Besides at least one compound of the formula I and at least one compound selected from the group consisting of compounds of the general formulae II to X, the medium according to the invention additionally

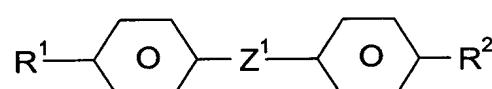
10 comprises one or more compounds selected from the group consisting of compounds of the general formulae XI to XVII:



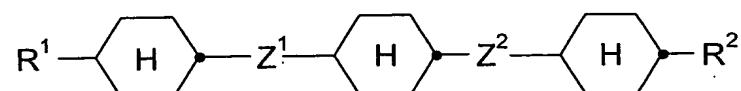
XI



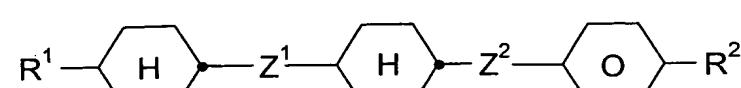
XII



XIII

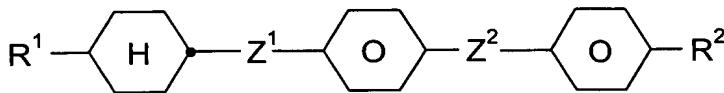


XIV

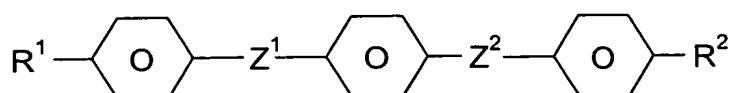


XV

- 26 -



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XVII

in which the individual radicals have the following meanings:

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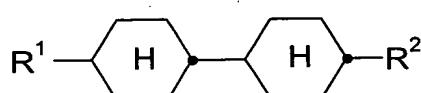
R^1 and R^2 : independently of one another, identically or differently, n-alkyl, n-alkoxy or alkenyl; each having up to 9 carbon atoms; and

15

Z^1 and Z^2 : independently of one another, identically or differently, a single bond, $-CF_2O-$, $-OCF_2-$, $-CH_2O-$, $-OCH_2-$, $-CO-O-$, $-O-CO-$, $-CH=CH-$, $-C_2H_4-$, $-C_2F_4-$, $-CH_2CF_2-$, $-CF_2CH_2-$ or $-C_4H_8-$, preferably each a single bond.

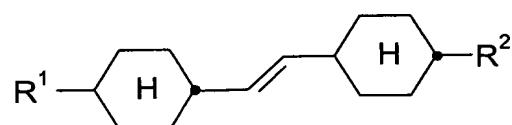
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The compound of the formula XI is preferably



XIa

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XIb

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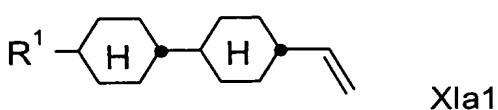
in which R^1 and R^2 can adopt the meanings indicated above. Preferably, however, R^1 is n-alkyl or alkenyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms or alkenyl having from 2 to 5 carbon atoms, and R^2 is alkenyl having up to 9 carbon atoms, particularly preferably alkenyl having from 2 to 5 carbon atoms.

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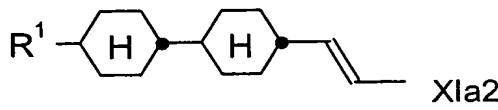
- 27 -

Particularly preferred compounds of the formula XIa are

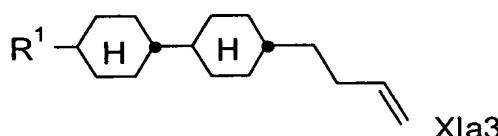
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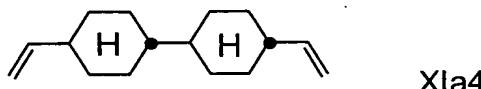
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15



25

in which R¹ can adopt the meanings indicated above, but is preferably n-alkyl having from 1 to 5 carbon atoms.

The compounds of the formulae XIa1 and XIa2 are particularly preferred.

25

The compound of the formula XII is preferably

30



in which R¹ and R² can adopt the meanings indicated above. Preferably, however, R¹ is n-alkyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms, and R² is alkoxy having up to

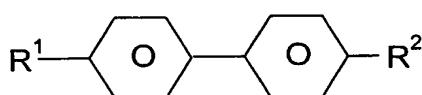
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- 28 -

9 carbon atoms, particularly preferably alkoxy having from 1 to 5 carbon atoms.

The compound of the formula XIII is preferably

5



XIIIa

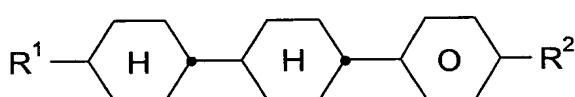
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in which R¹ and R² can adopt the meanings indicated above. Preferably, however, R¹ is n-alkyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms, and R² is alkenyl having up to 9 carbon atoms, particularly preferably alkenyl having from 2 to 5 carbon atoms.

15

The compound of the formula XV is preferably

20



XVa

25

in which R¹ and R² can adopt the meanings indicated above. Preferably, however, R¹ is alkenyl having up to 9 carbon atoms, particularly preferably alkenyl having from 2 to 5 carbon atoms, and R² is n-alkyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms.

Particularly preferred embodiments are indicated below.

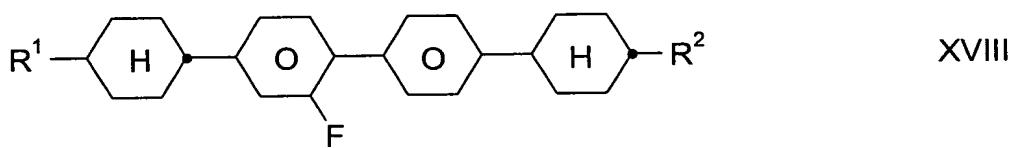
- The medium comprises one or more compounds of the formulae XI, XII, XIII, XIV, XV, XVI and/or XVII; preferably one or more compounds of the formulae XIa, XIb, XIIa, XIIIa and/or XVa.
- The proportion of compounds of the formulae XI to XVII in the mixture as a whole is from 5 to 70% by weight, preferably from 10 to 60% by

weight and particularly preferably either from 10 to 30% by weight (embodiment B) or from 35 to 55% by weight (embodiment A).

- The proportion of compounds of the formulae I to XVII together in the mixture as a whole is at least 50% by weight, preferably at least 70%
- 5 by weight and particularly preferably at least 90% by weight.
- The medium essentially consists of compounds of the formulae I to XVII.
- 10 The total amount of compounds of the formulae I to XVII in the mixtures according to the invention is not crucial. The mixtures may therefore comprise one or more further components in order to optimise various properties. However, the observed effect on the rotational viscosity and the optical anisotropy is generally greater the higher the total concentration of
- 15 compounds of the formulae I to XVII.

Furthermore, the medium according to the invention may additionally comprise one or more compounds selected from compounds of the general formula XVIII:

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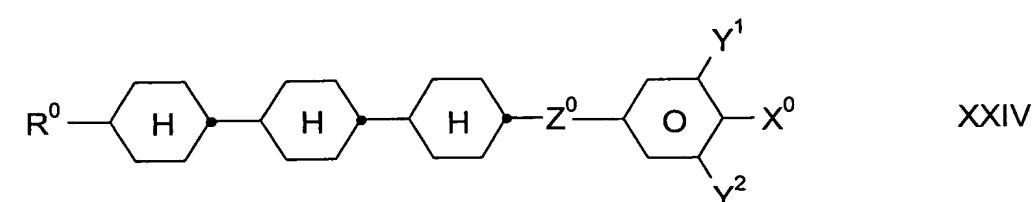
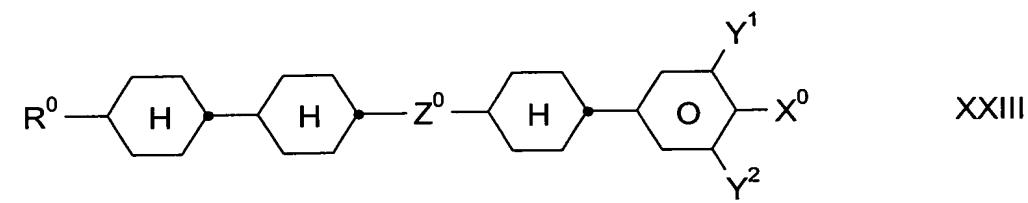
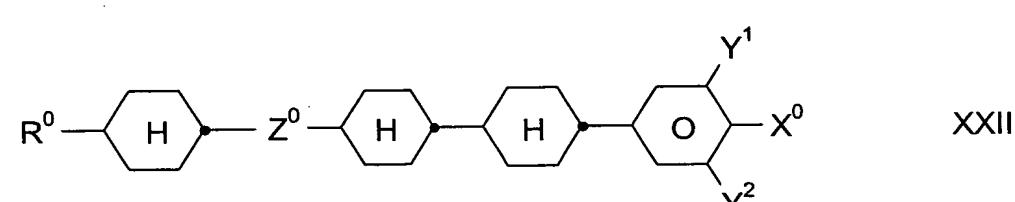
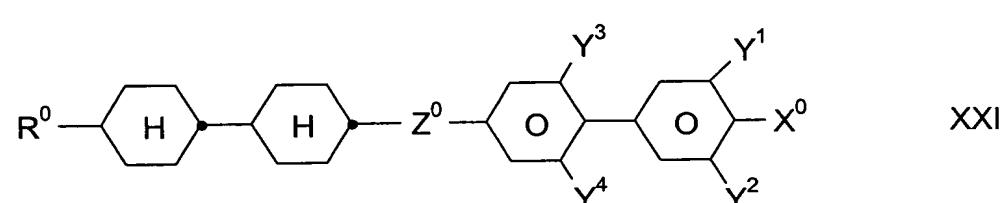
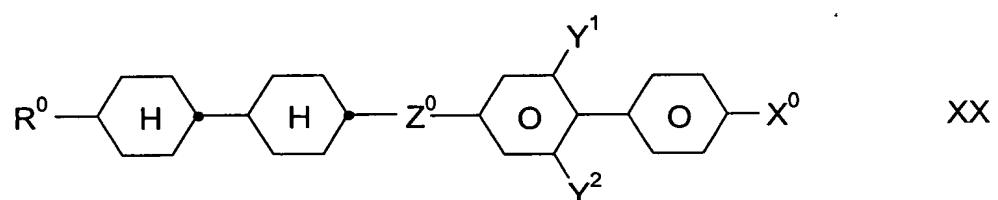
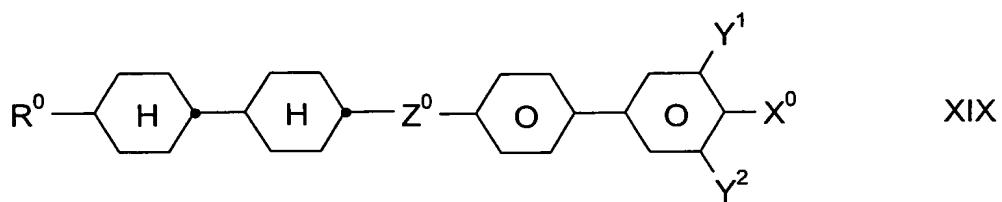
in which R¹ and R² can adopt the meanings indicated above. Preferably, however, R¹ and R² are n-alkyl having up to 9 carbon atoms, particularly preferably n-alkyl having from 1 to 5 carbon atoms.

The proportion of compounds of the formula XVIII in the mixture as a whole can be up to 10% by weight.

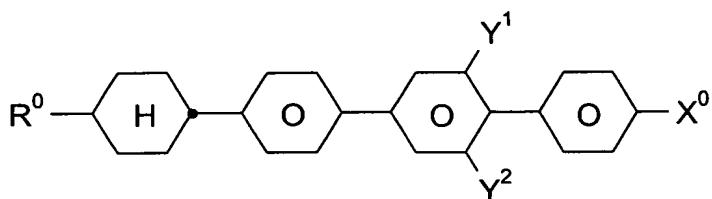
30

In addition, the medium according to the invention may additionally comprise one or more compounds selected from the group consisting of compounds of the general formulae XIX to XXVI:

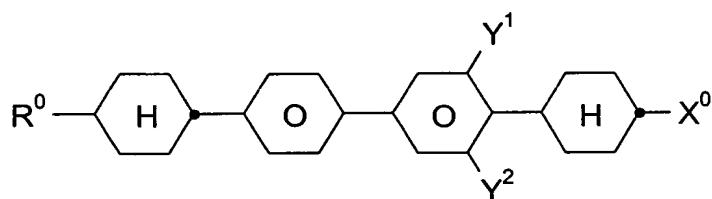
- 30 -



- 31 -



5



10

in which R^0 , X^0 , Y^1 , Y^2 , Y^3 , Y^4 and Z^0 each, independently of one another,
 have one of the meanings indicated above. Preferably, X^0 is F, Cl, CF_3 ,
 15 OCF_3 or $OCHF_2$. R^0 is preferably alkyl, oxaalkyl, fluoroalkyl or alkenyl, each
 having up to 6 carbon atoms, and Z^0 is preferably a single bond or
 $-CH_2-CH_2-$. Y^1 , Y^2 , Y^3 and Y^4 are each, independently of one another, H or
 F.

20

The individual compounds of the formulae II to XXVI and their sub-formulae which can be used in the media according to the invention are either known or can be prepared analogously to known compounds.

25

It has been found that even a relatively small proportion of compounds of the formula I mixed with conventional liquid-crystal materials, but in particular with one or more compounds of the formulae II, III, IV, V, VI, VII, VIII, IX and/or X, results in a significant reduction in the rotational viscosity γ_1 and in higher values for the optical anisotropy Δn , enabling shorter response times of the displays to be achieved, with broad nematic phases having low smectic-nematic transition temperatures being observed at the same time, causing an improvement in the storage stability. The compounds of the formulae I to X are colourless, stable and readily miscible with one another and with other liquid-crystal materials. The

35

mixtures according to the invention are furthermore distinguished by very high clearing points.

The construction of the MLC display according to the invention from polarisers, electrode base plates and electrodes having a surface

5 treatment corresponds to the conventional design for displays of this type. The term conventional design here is broadly drawn and also covers all derivatives and modifications of the MLC display, in particular also matrix display elements based on poly-Si TFT or MIM.

10 An essential difference between the displays according to the invention and the hitherto conventional displays based on the twisted nematic cell consists, however, in the choice of the liquid-crystal parameters of the liquid-crystal layer.

15 The liquid-crystal mixtures which can be used in accordance with the invention are prepared in a manner conventional per se. In general, the desired amount of the components used in lesser amount is dissolved in the components making up the principal constituent, preferably at elevated temperature. It is also possible to mix solutions of the components in an
20 organic solvent, for example in acetone, chloroform or methanol, and to remove the solvent again, for example by distillation, after mixing.

The dielectrics may also comprise further additives known to the person skilled in the art and described in the literature. For example, from 0 to
25 15% of pleochroic dyes and/or chiral dopants may be added.

In the present application and in the following examples, the structures of the liquid-crystal compounds are indicated by means of acronyms, with the transformation into chemical formulae taking place in accordance with
30 Tables A and B below. All radicals C_nH_{2n+1} and C_mH_{2m+1} are straight-chain alkyl radicals having n and m carbon atoms respectively; n and m are preferably 0, 1, 2, 3, 4, 5, 6 or 7. The coding in Table B is self-evident. In Table A, only the acronym for the parent structure is indicated. In individual cases, the acronym for the parent structure is followed, separated by a
35 dash, by a code for the substituents R^1 , R^2 , L^1 and L^2 .

- 33 -

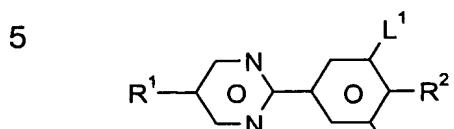
	Code for R ¹ , R ² , L ¹ , L ²	R ¹	R ²	L ¹	L ²
5	nm	C _n H _{2n+1}	C _m H _{2m+1}	H	H
	nOm	C _n H _{2n+1}	OC _m H _{2m+1}	H	H
	nO.m	OC _n H _{2n+1}	C _m H _{2m+1}	H	H
	n	C _n H _{2n+1}	CN	H	H
	nN.F	C _n H _{2n+1}	CN	H	F
10	nF	C _n H _{2n+1}	F	H	H
	nOF	OC _n H _{2n+1}	F	H	H
	nCl	C _n H _{2n+1}	Cl	H	H
	nF.F	C _n H _{2n+1}	F	H	F
	nF.F.F	C _n H _{2n+1}	F	F	F
15	nCF ₃	C _n H _{2n+1}	CF ₃	H	H
	nOCF ₃	C _n H _{2n+1}	OCF ₃	H	H
	nOCF ₂	C _n H _{2n+1}	OCHF ₂	H	H
	nS	C _n H _{2n+1}	NCS	H	H
	rVsN	C _r H _{2r+1} -CH=CH-C _s H _{2s-}	CN	H	H
20	rEsN	C _r H _{2r+1} -O-C _s H _{2s-}	CN	H	H
	nAm	C _n H _{2n+1}	COOC _m H _{2m+1}	H	H
	nOCCF ₂ .F.F	C _n H _{2n+1}	OCH ₂ CHF ₂	F	F
	V-n	CH ₂ =CH	C _n H _{2n+1}	H	H
	25				

30

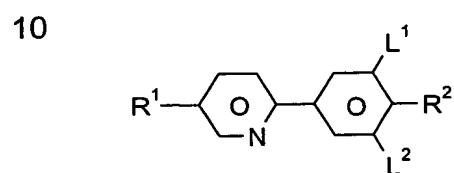
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Preferred mixture components of the mixture concept according to the invention are shown in Tables A and B:

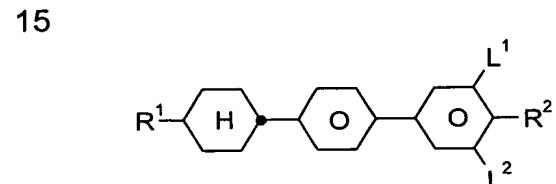
Table A:



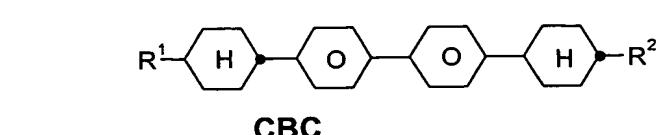
PYP



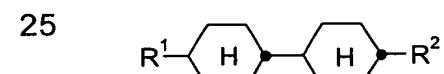
PYRP



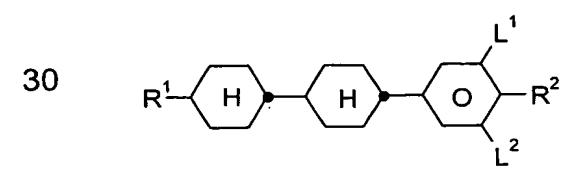
BCH



CBC

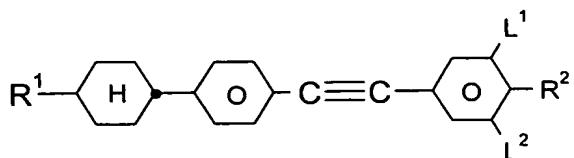


CCH

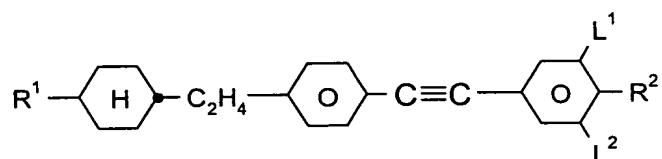


CCP

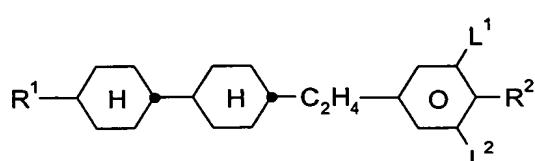
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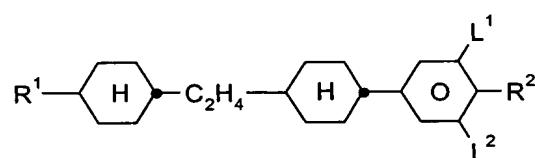
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**CEPTP**

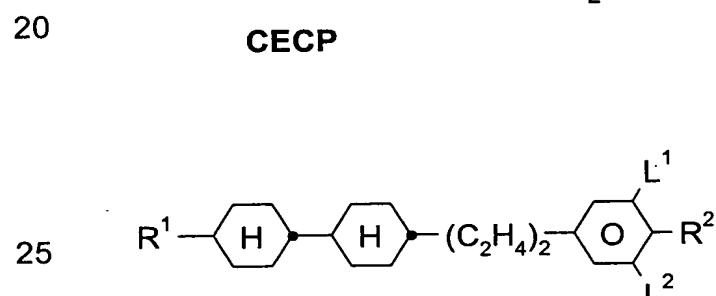
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**ECCP**

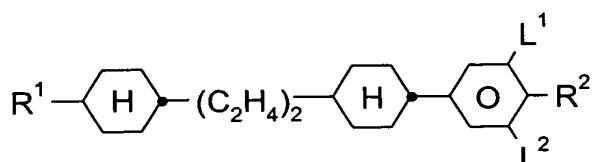
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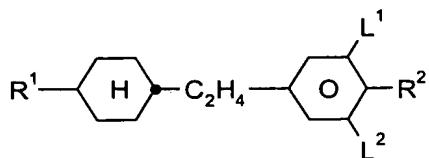
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CECP**CCEEP**

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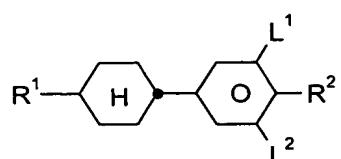
**CEECP**

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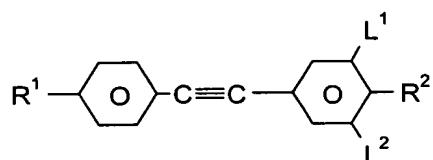
EPCH

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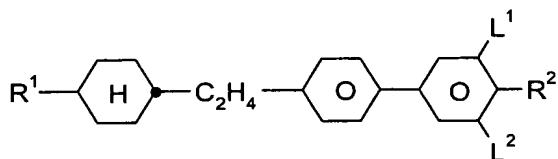
PCH

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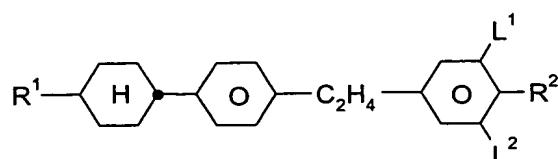
PTP

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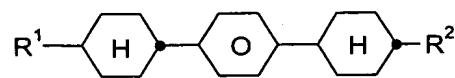
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BECH



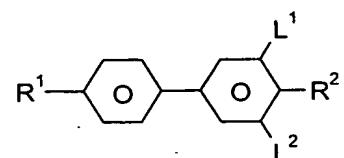
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EBCH



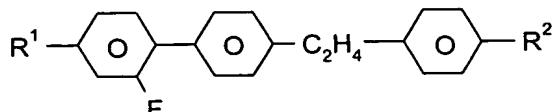
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CPC

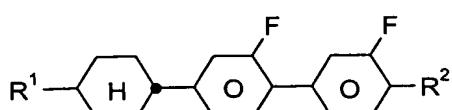


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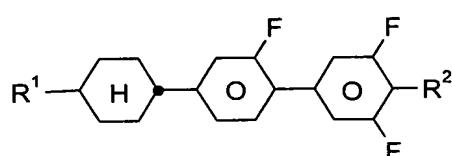
B

**FET**

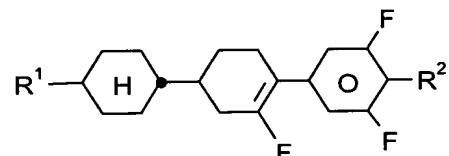
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**CGG**

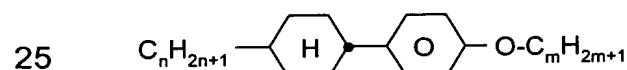
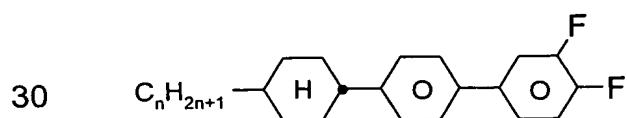
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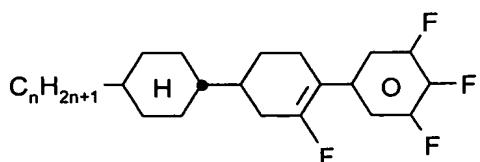
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**CFU**

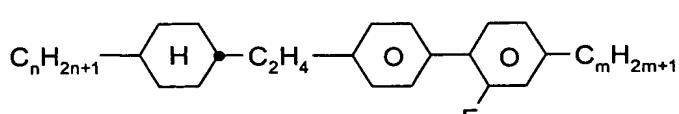
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Table B:**PCH-nOm****BCH-nF.F**

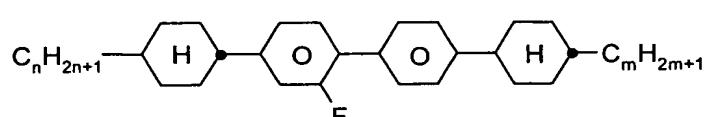
- 38 -



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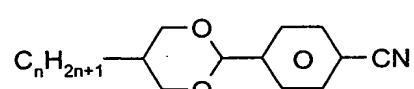


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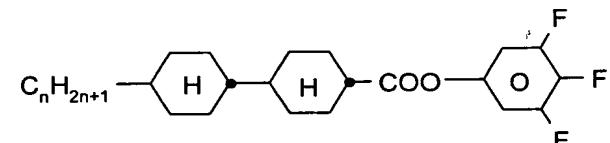
CBC-nmF

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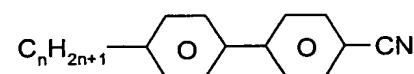
PDX-n

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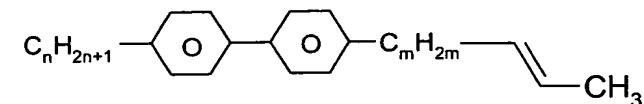
CCZU-n-F

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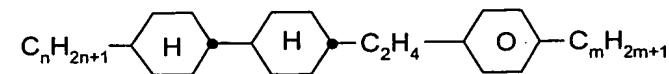
K3n

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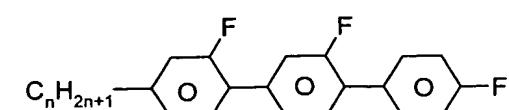
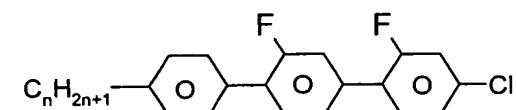
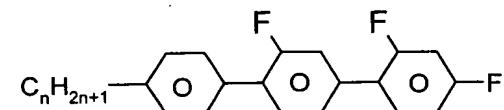
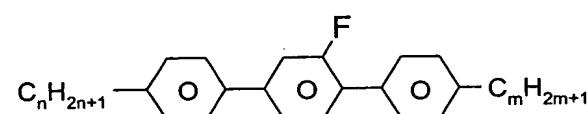
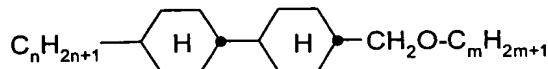
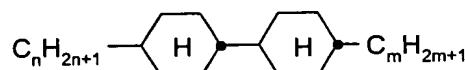
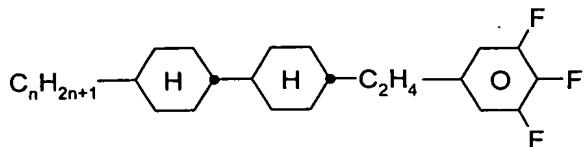


PP-n-mV1

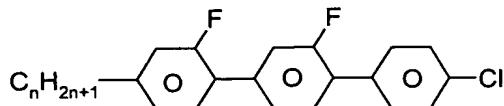
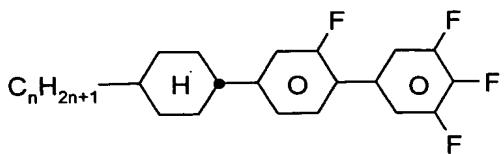
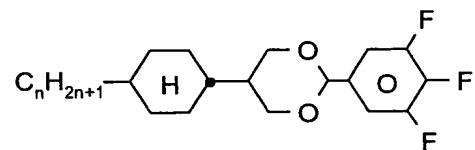
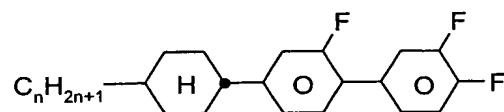
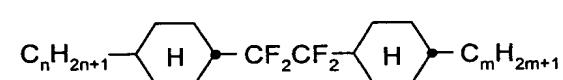
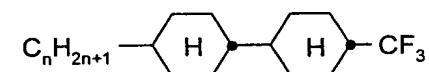
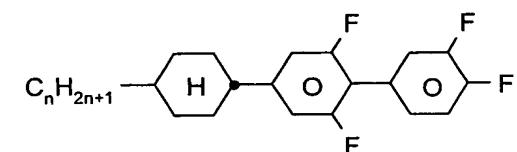
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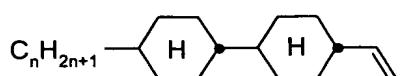
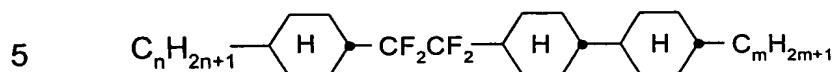
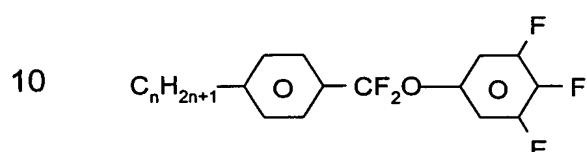
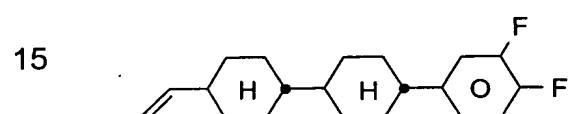
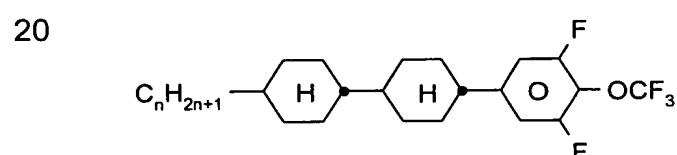
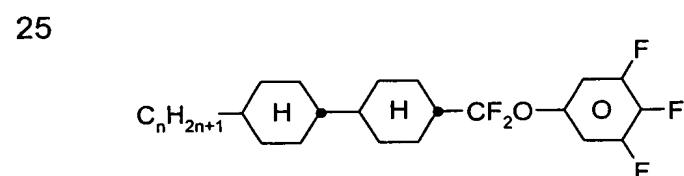
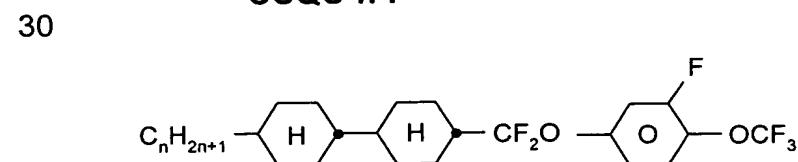
ECCP-nm



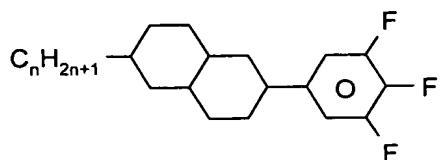
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**GGP-n-Cl****CGU-n-F****CDU-n-F****CGG-n-F****CWC-n-m****CCH-nCF₃****CUP-nF.F**

- 41 -

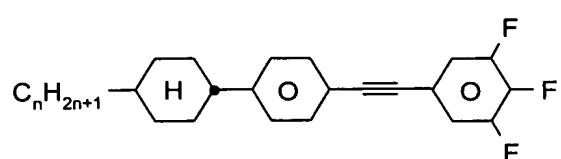
**CC-n-V****CWCC-n-m****PQU-n-F****CCG-V-F****CCU-n-OT****CCQU-n-F****CCQG-n-OT**

- 42 -



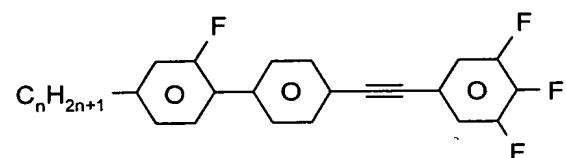
Dec-U-n-F

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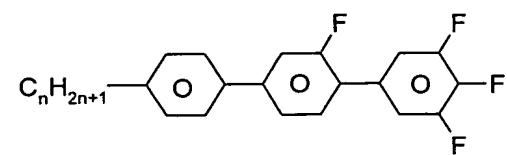
CPTU-n-F

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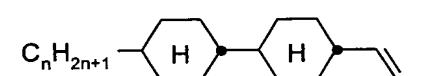
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GPTU-n-F



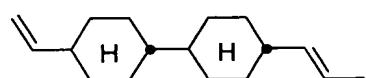
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PGU-n-F



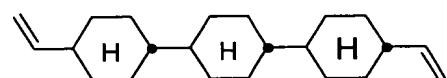
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CC-n-V1



CC-V-V1

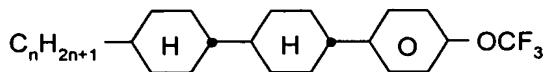
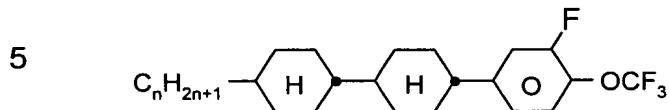
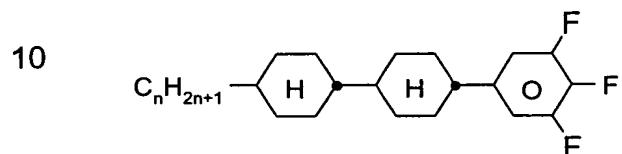
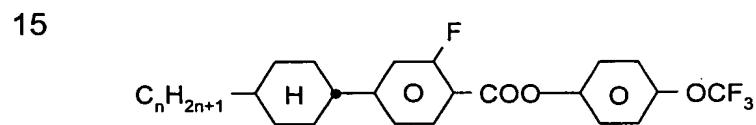
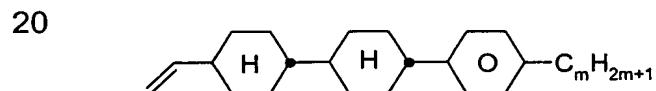
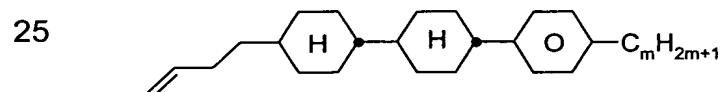
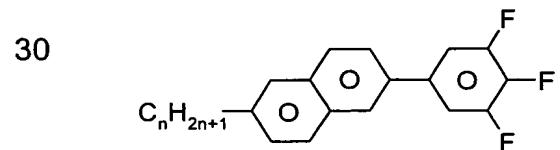
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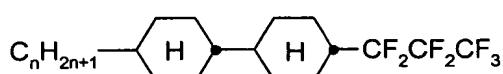
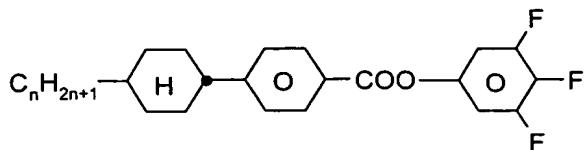
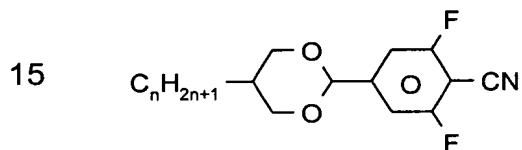
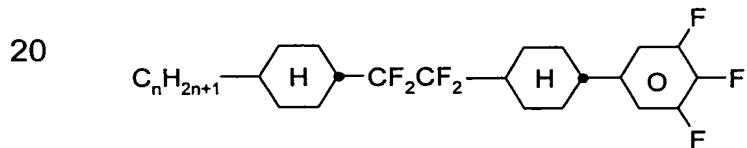
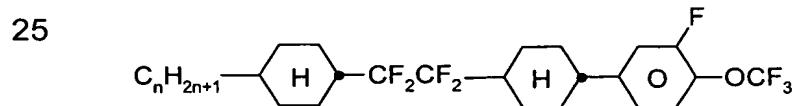
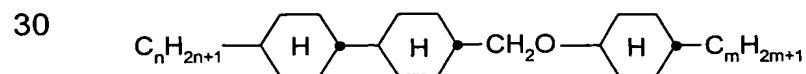
CCC-V-V

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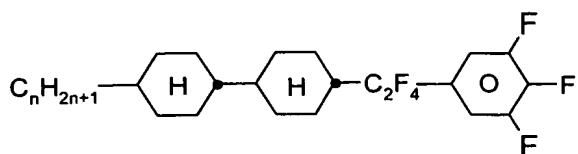
- 43 -

**CCP-nOCF₃****CCP-nOCF₃.F****CCP-nF.F.F****CGZP-n-OT****CCP-V-m****CCP-V2-m****Nap-U-n-F**

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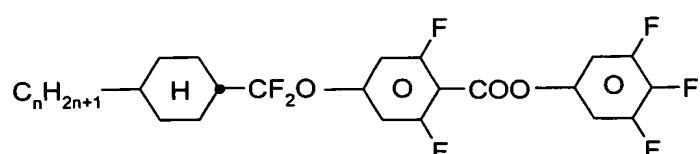
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- 45 -



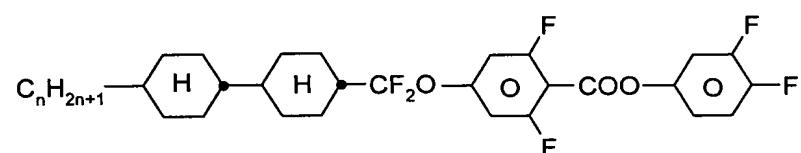
CCWU-n-F

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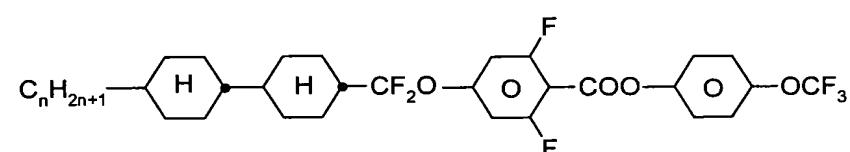


CQUZU-n-F

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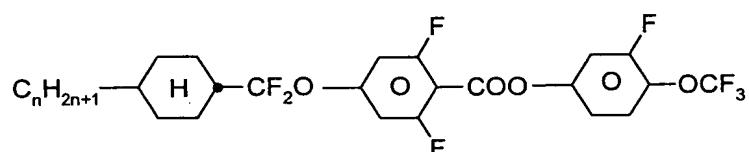


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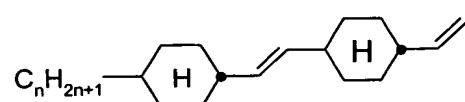
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CCQUZP-n-OT



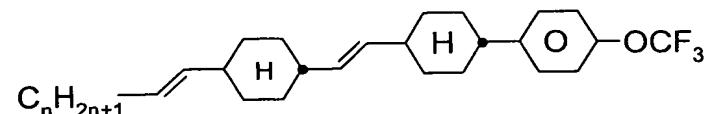
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CQUZG-n-OT



CVC-n-V

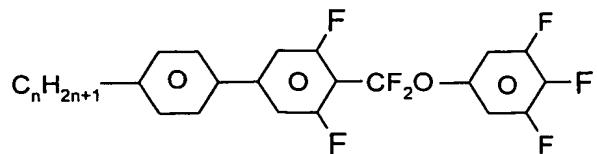
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CVCP-nV-OT

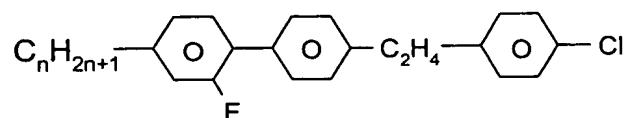
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PUQU-n-F

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FET-nCl

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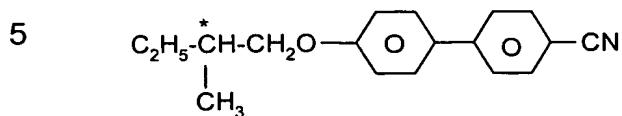
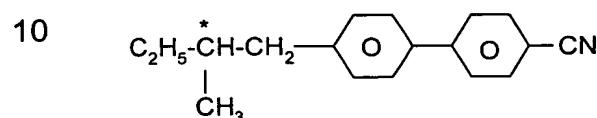
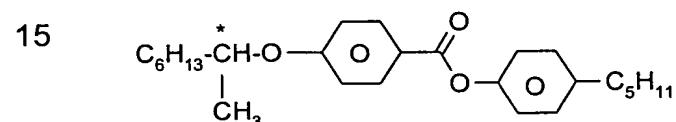
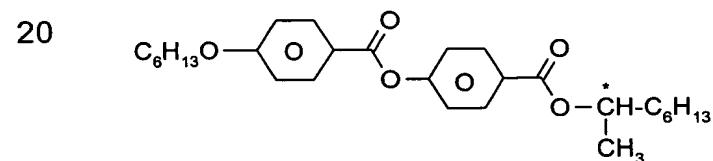
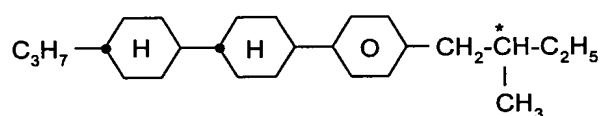
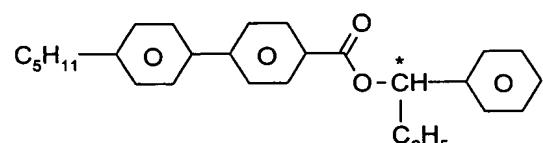
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Table C:

Table C shows possible dopants which are preferably added to the mixtures according to the invention.

**C 15****CB 15****CM 21****R/S-811****CM 44****CM 45**

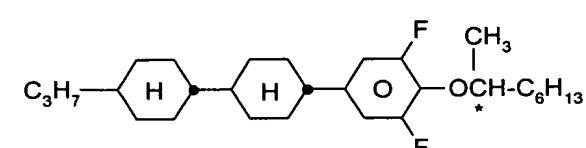
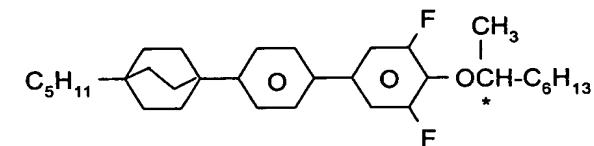
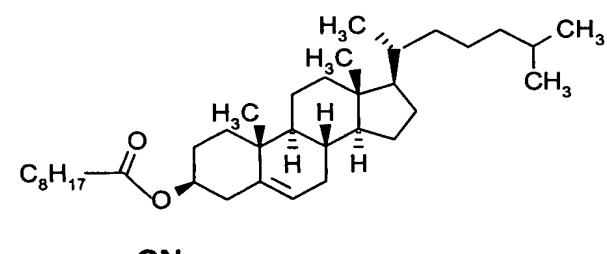
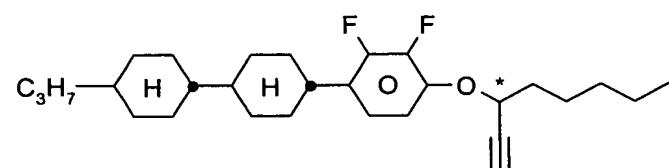
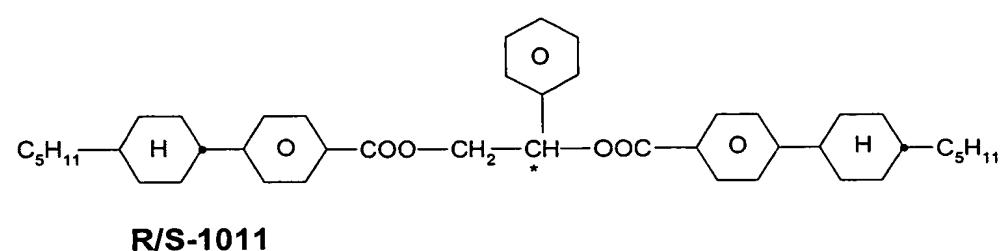
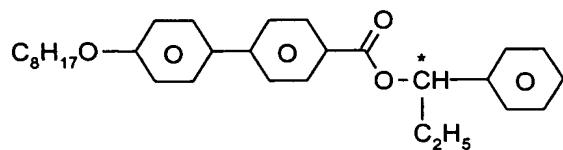
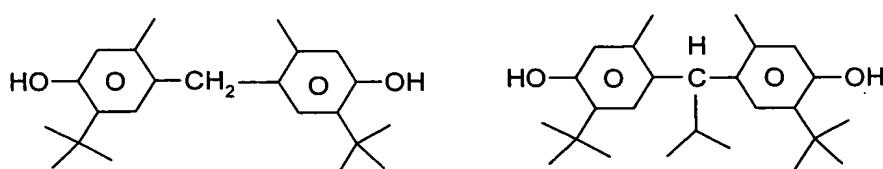


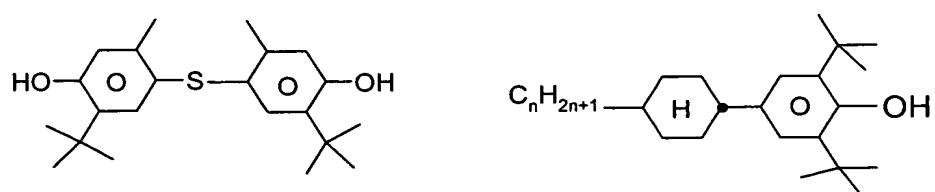
Table D:

Stabilisers which can be added, for example, to the mixtures according to the invention are mentioned below.

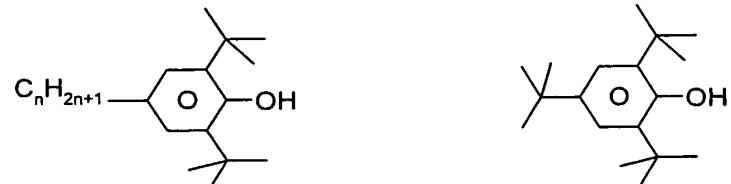
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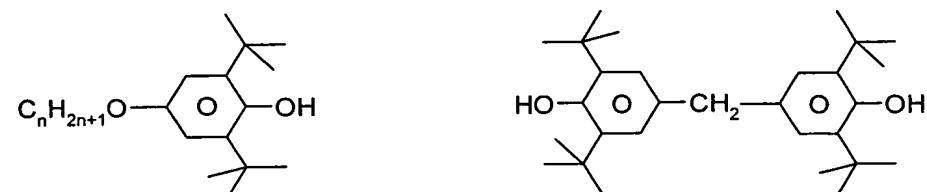
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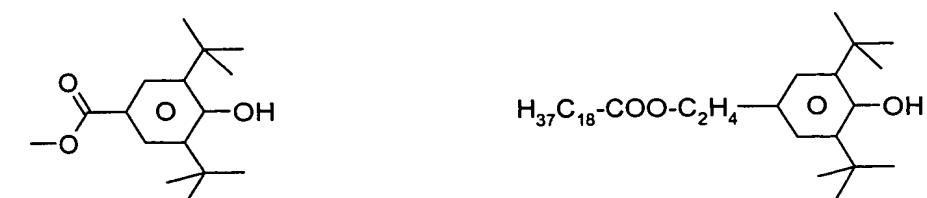
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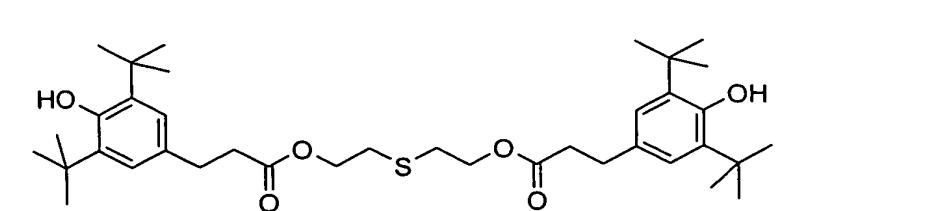
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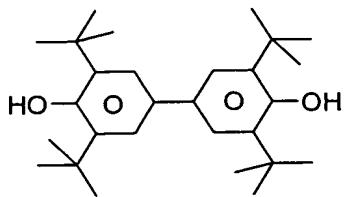


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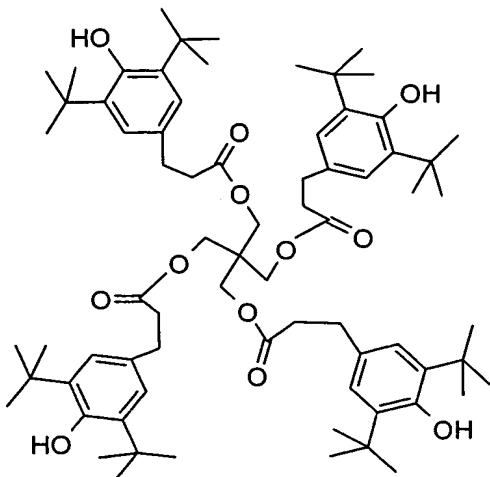


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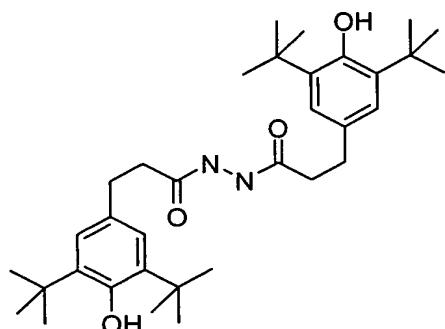
- 50 -



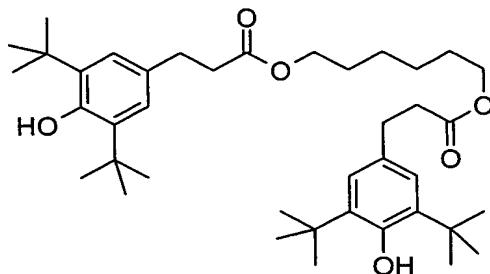
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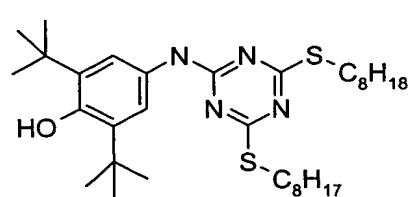
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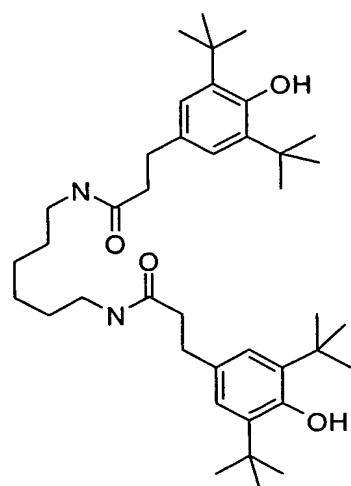
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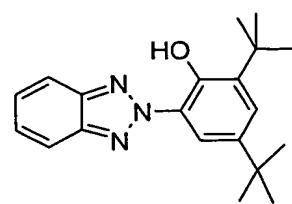
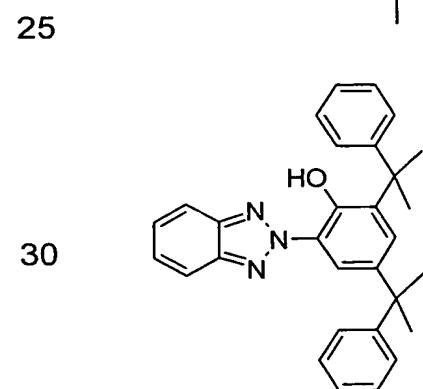
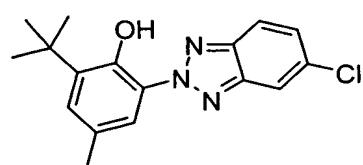
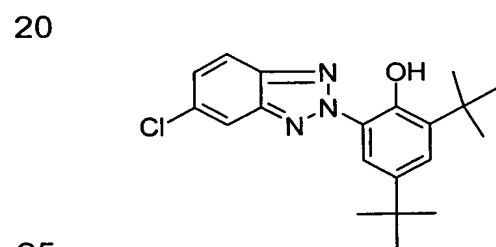
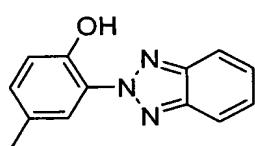
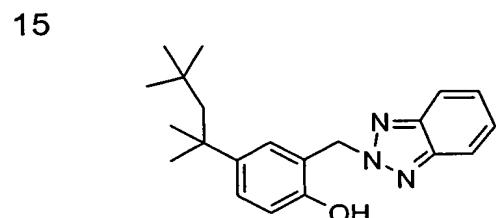
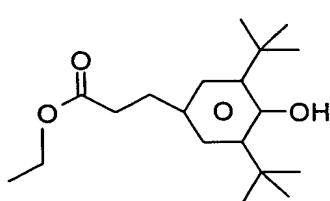
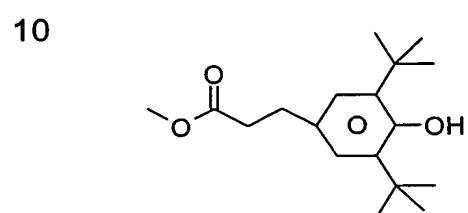
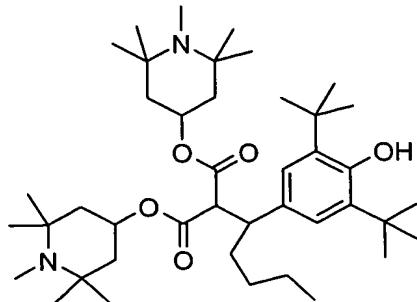
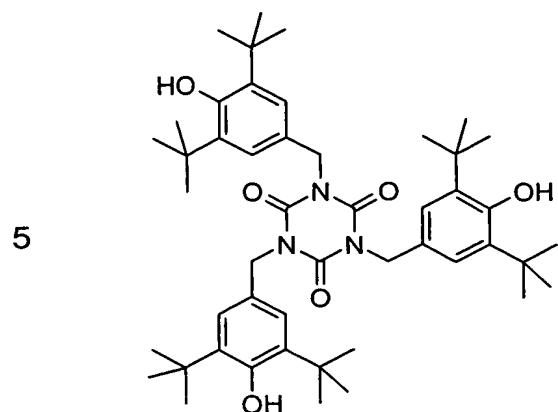
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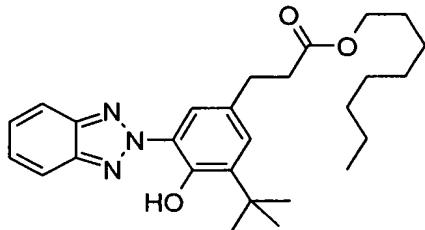
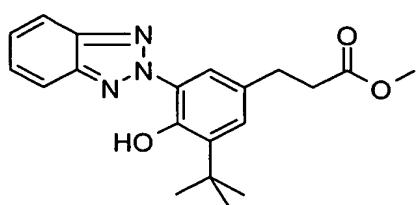
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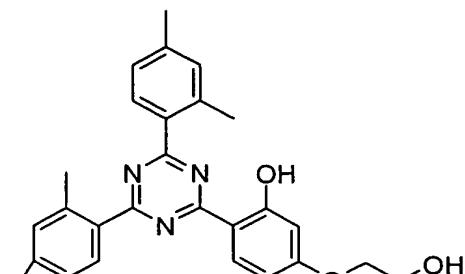
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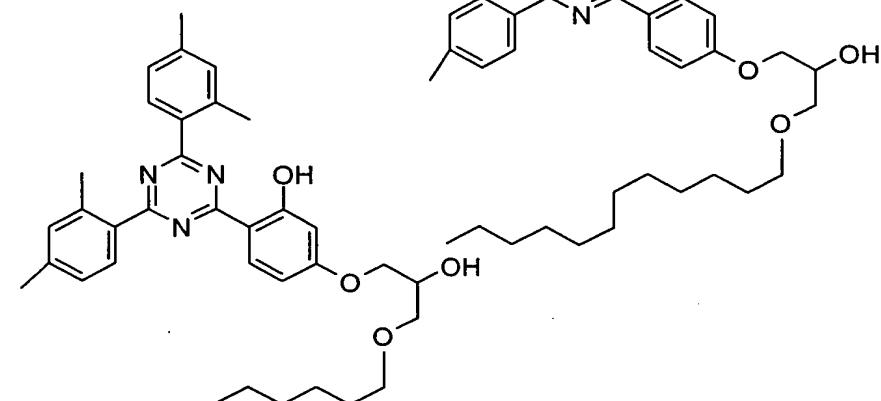
- 52 -



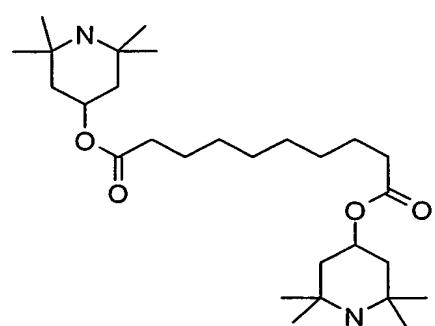
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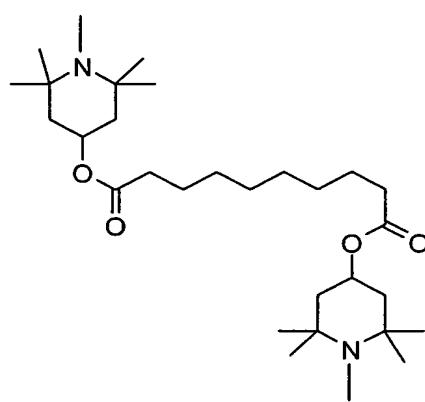
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Besides one or more compounds of the formula I, particularly preferred mixtures comprise one, two, three, four, five or more compounds from Table B.

5 The following examples are intended to explain the invention without restricting it. Above and below, percentages are per cent by weight. All temperatures are indicated in degrees Celsius. cl.p. denotes clearing point.

10 Δn denotes the optical anisotropy (589 nm, 20°C). The optical data were measured at 20°C, unless expressly stated otherwise. $\Delta \epsilon$ denotes the dielectric anisotropy ($\Delta \epsilon = \epsilon_{\parallel} - \epsilon_{\perp}$, where ϵ_{\parallel} denotes the dielectric constant parallel to the longitudinal molecular axes and ϵ_{\perp} denotes the dielectric constant perpendicular thereto). The electro-optical data were measured in a TN cell at the 1st minimum (i.e. at a $d \cdot \Delta n$ value of 0.5 µm) at 20°C, unless expressly stated otherwise. The rotational viscosity γ_1 (mPa·s) was
15 determined at 20°C.

20 V_{10} denotes the threshold voltage, i.e. the characteristic voltage at a relative contrast of 10%, V_{50} denotes the characteristic voltage at a relative contrast of 50% and V_{90} denotes the characteristic voltage at a relative contrast of 90%. V_0 denotes the capacitive threshold voltage. The twist is 90°, unless indicated otherwise.

The elastic constants K_1 and K_3 were determined at 20°C. K_3/K_1 is the ratio of the elastic constants K_3 and K_1 .

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Examples

Example 1

5 10 15	CCP-20CF ₃	2.0%	Clearing point [°C]:	80.0
	CCP-30CF ₃	8.0%	Δn [589 nm, 20°C]:	0.0934
	CCZU-3-F	14.0%	Δε [1 kHz, 20°C]:	6.0
	CC-3-V1	10.0%	γ ₁ [mPa·s, 20°C]:	70
	PCH-301	7.0%	V ₁₀ [V]:	1.64
	CCP-V-1	12.0%	V ₅₀ [V]:	1.99
	CCG-V-F	10.0%	V ₉₀ [V]:	2.48
	CC-4-V	18.0%	V ₉₀ /V ₁₀ :	1.509
	PUQU-2-F	6.0%		
	PUQU-3-F	8.0%		
	PGP-2-3	5.0%		

Example 2

20 25 30	CCP-20CF ₃	4.0%	Clearing point [°C]:	79.0
	CCP-30CF ₃	8.0%	Δn [589 nm, 20°C]:	0.0960
	CCZU-3-F	14.0%		
	CC-3-V1	10.0%		
	PCH-301	9.0%		
	CCP-V-1	16.0%		
	CC-4-V	18.0%		
	PUQU-1-F	8.0%		
	PUQU-2-F	7.0%		
	PGP-3-2	6.0%		

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Example 3

CCP-20CF ₃	2.0%	Clearing point [°C]:	81.5
CCP-30CF ₃	8.0%	Δn [589 nm, 20°C]:	0.0940
CCZU-3-F	14.0%	Δε [1 kHz, 20°C]:	6.2
CC-3-V1	10.0%	γ ₁ [mPa·s, 20°C]:	70
PCH-301	6.0%	V ₁₀ [V]:	1.67
CCP-V-1	13.0%	V ₅₀ [V]:	2.02
CCG-V-F	10.0%	V ₉₀ [V]:	2.53
CC-4-V	18.0%	V ₉₀ /V ₁₀ :	1.512
PUQU-1-F	8.0%		
PUQU-2-F	6.0%		
PGP-3-2	5.0%		

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Example 4

CCP-30CF ₃	8.0%	Clearing point [°C]:	82.0
CCZU-3-F	13.0%	Δn [589 nm, 20°C]:	0.0925
CC-3-V1	10.0%	Δε [1 kHz, 20°C]:	6.1
CCP-V-1	13.0%		
CCG-V-F	10.0%		
CC-4-V	18.0%		
PUQU-1-F	8.0%		
PUQU-2-F	7.0%		
PGP-3-2	5.0%		
CVC-3-V	8.0%		

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Example 5

PGU-2-F	2.0%	Clearing point [°C]:	80.5
CCP-20CF ₃	7.0%	Δn [589 nm, 20°C]:	0.0942
CCP-30CF ₃	7.0%	V ₁₀ [V]:	1.65
CCZU-3-F	14.0%		
CC-3-V1	10.0%		
PCH-301	3.0%		
CCP-V-1	10.0%		
CCG-V-F	10.0%		
CC-4-V	18.0%		
PUQU-2-F	6.0%		
PUQU-3-F	8.0%		
PGP-2-4	5.0%		

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Example 6

PGU-2-F	7.0%	Clearing point [°C]:	79.0
CC-3-V1	10.0%	Δn [589 nm, 20°C]:	0.1036
CCP-V-1	12.0%	Δε [1 kHz, 20°C]:	5.0
CCP-V2-1	3.0%	γ ₁ [mPa·s, 20°C]:	67
CCG-V-F	10.0%	V ₁₀ [V]:	1.78
CCP-20CF ₃	4.0%	V ₅₀ [V]:	2.13
CCP-30CF ₃	4.0%	V ₉₀ [V]:	2.65
CCP-40CF ₃	2.0%	V ₉₀ /V ₁₀ :	1.490
CCZU-3-F	5.0%		
PCH-301	8.0%		
CC-4-V	18.0%		
PUQU-2-F	4.0%		
PUQU-3-F	5.0%		
PGP-2-4	8.0%		

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Example 7

CC-4-V	18.0%	Clearing point [°C]:	79.5
CC-3-V1	11.0%	Δn [589 nm, 20°C]:	0.0939
PCH-302	9.0%	Δε [1 kHz, 20°C]:	6.0
CCP-20CF ₃	7.5%	γ ₁ [mPa·s, 20°C]:	71
CCP-30CF ₃	8.0%	V ₁₀ [V]:	1.80
CCZU-3-F	13.0%	V ₅₀ [V]:	2.15
PGP-2-3	5.5%	V ₉₀ [V]:	2.65
PGP-2-4	5.0%	V ₉₀ /V ₁₀ :	1.474
CCQU-2-F	6.0%		
CCQU-3-F	10.0%		
PUQU-2-F	3.0%		
PUQU-3-F	4.0%		

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Example 8

CCP-20CF ₃	4.0%	Clearing point [°C]:	79.0
CCP-30CF ₃	4.0%	Δn [589 nm, 20°C]:	0.0927
CCP-40CF ₃	4.0%	Δε [1 kHz, 20°C]:	5.1
CCZU-3-F	9.0%	γ ₁ [mPa·s, 20°C]:	65
CC-3-V1	10.0%	V ₁₀ [V]:	1.76
PCH-301	9.0%	V ₅₀ [V]:	2.13
CCP-V-1	14.0%	V ₉₀ [V]:	2.66
CCG-V-F	10.0%	V ₉₀ /V ₁₀ :	1.513
CC-4-V	18.0%		
PUQU-2-F	6.0%		
PUQU-3-F	7.0%		
PGP-2-3	5.0%		

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Example 9

5 10	CCP-30CF ₃	7.0%	Clearing point [°C]:	79.5
	CCZU-2-F	2.0%	Δn [589 nm, 20°C]:	0.0947
	CCZU-3-F	14.0%	Δε [1 kHz, 20°C]:	6.0
	PUQU-2-F	6.0%	γ ₁ [mPa·s, 20°C]:	68
	PUQU-3-F	8.0%	V ₁₀ [V]:	1.72
	CCP-V-1	8.0%		
	CC-3-V1	12.0%		
	CC-4-V	18.0%		
	PCH-301	10.0%		
	PGP-2-3	6.0%		
	CVCP-1V-OT	9.0%		

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Example 10

20 25	CCZU-2-F	3.0%	Clearing point [°C]:	79.0
	CCZU-3-F	14.0%	Δn [589 nm, 20°C]:	0.0935
	PCH-302	10.0%	Δε [1 kHz, 20°C]:	6.1
	CCP-V-1	9.0%	γ ₁ [mPa·s, 20°C]:	70
	CCG-V-F	5.0%	V ₁₀ [V]:	1.67
	CC-3-V1	12.0%		
	CC-4-V	18.0%		
	PUQU-2-F	6.0%		
	PUQU-3-F	8.0%		
	PGP-2-3	5.0%		
	CVCP-1V-OT	10.0%		

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Example 11

PGU-2-F	4.0%	Clearing point [°C]:	80.5
CC-3-V1	10.0%	γ_1 [mPa·s, 20°C]:	67
CCP-V-1	14.0%	V_{10} [V]:	1.80
CCG-V-F	10.0%		
CCP-20CF ₃	6.0%		
CCP-30CF ₃	6.0%		
CCP-40CF ₃	4.0%		
PCH-301	6.0%		
CC-4-V	18.0%		
PUQU-2-F	6.0%		
PUQU-3-F	8.0%		
PGP-2-3	8.0%		

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Example 12

PGU-2-F	6.0%	Clearing point [°C]:	80.0
PGU-3-F	2.0%	Δn [589 nm, 20°C]:	0.1048
CC-3-V1	11.0%	$\Delta \epsilon$ [1 kHz, 20°C]:	5.7
CCP-V-1	12.0%	γ_1 [mPa·s, 20°C]:	69
CCG-V-F	10.0%	V_{10} [V]:	1.68
CCP-30CF ₃	6.0%	V_{50} [V]:	2.02
CCZU-3-F	12.0%	V_{90} [V]:	2.48
PCH-301	7.0%	V_{90}/V_{10} :	1.478
CC-4-V	18.0%		
PUQU-2-F	4.0%		
PUQU-3-F	4.0%		
PGP-2-3	8.0%		

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Example 13

CCZU-2-F	3.0%	Clearing point [°C]:	80.0
CCZU-3-F	14.0%	Δn [589 nm, 20°C]:	0.0934
PUQU-2-F	6.0%	Δε [1 kHz, 20°C]:	6.1
PUQU-3-F	8.0%	γ ₁ [mPa·s, 20°C]:	69
CCG-V-F	9.0%	V ₁₀ [V]:	1.67
CCP-V-1	12.0%	V ₅₀ [V]:	2.01
CC-3-V1	13.0%	V ₉₀ [V]:	2.52
CC-4-V	18.0%	V ₉₀ /V ₁₀ :	1.511
PCH-301	5.0%		
PGP-2-4	6.0%		
CVCP-2V-OT	6.0%		

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Example 14

PUQU-2-F	10.0%	Clearing point [°C]:	79.0
PUQU-3-F	10.0%	Δn [589 nm, 20°C]:	0.0943
CCP-V-1	16.0%	Δε [1 kHz, 20°C]:	5.6
CCP-V2-1	4.0%	γ ₁ [mPa·s, 20°C]:	67
CCG-V-F	10.0%	V ₁₀ [V]:	1.78
CC-3-V1	13.0%	V ₅₀ [V]:	2.15
CC-4-V	18.0%	V ₉₀ [V]:	2.71
PCH-301	6.0%	V ₉₀ /V ₁₀ :	1.522
PGP-2-4	2.0%		
CVCP-1V-OT	11.0%		

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Example 15

CCZU-3-F	6.0%	Clearing point [°C]:	79.0
CCP-V-1	16.0%	Δn [589 nm, 20°C]:	0.0940
CCG-V-F	10.0%	Δε [1 kHz, 20°C]:	5.8
CC-4-V	18.0%	γ ₁ [mPa·s, 20°C]:	65
CC-3-V1	13.0%	V ₁₀ [V]:	1.71
PCH-301	6.0%	V ₅₀ [V]:	2.06
PUQU-1-F	9.0%	V ₉₀ [V]:	2.59
PUQU-2-F	9.0%	V ₉₀ /V ₁₀ :	1.519
PGP-2-4	3.0%		
CVCP-1V-OT	10.0%		

Example 16

CCZU-3-F	12.0%	Clearing point [°C]:	79.0
PUQU-2-F	8.0%	Δn [589 nm, 20°C]:	0.0938
PUQU-3-F	9.0%	Δε [1 kHz, 20°C]:	5.8
CCP-V-1	12.0%	γ ₁ [mPa·s, 20°C]:	68
CC-3-V1	12.0%	V ₁₀ [V]:	1.72
CC-4-V	18.0%	V ₅₀ [V]:	2.08
PCH-301	11.0%	V ₉₀ [V]:	2.59
PGP-2-3	4.0%	V ₉₀ /V ₁₀ :	1.506
CVCP-1V-OT	10.0%		
CCC-V-V	4.0%		

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Example 17

5 10	CCZU-3-F	7.0%	Clearing point [°C]:	80.0
	CCP-V-1	16.0%	Δn [589 nm, 20°C]:	0.0936
	CCG-V-F	10.0%	Δε [1 kHz, 20°C]:	5.9
	CC-4-V	18.0%	γ ₁ [mPa·s, 20°C]:	67
	CC-3-V1	13.0%	V ₁₀ [V]:	1.71
	PCH-301	5.0%	V ₅₀ [V]:	2.07
	PUQU-2-F	9.0%	V ₉₀ [V]:	2.60
	PUQU-3-F	9.0%	V ₉₀ /V ₁₀ :	1.518
	PGP-2-4	3.0%		
	CVCP-1V-OT	10.0%		

Example 18

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15 20 25	CCZU-2-F	4.0%	Clearing point [°C]:	80.0
	CCZU-3-F	14.0%	Δn [589 nm, 20°C]:	0.0941
	CCP-20CF3	4.0%	Δε [1 kHz, 20°C]:	7.4
	CCP-30CF3	3.0%	γ ₁ [mPa·s, 20°C]:	66
	CCP-V-1	14.0%	V ₁₀ [V]:	1.55
	CCG-V-F	5.0%	V ₅₀ [V]:	1.87
	PUQU-1-F	10.0%	V ₉₀ [V]:	2.33
	PUQU-2-F	8.0%	V ₉₀ /V ₁₀ :	1.505
	PGP-2-4	5.0%		
	CC-3-V1	13.0%		

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Example 19

PGU-1-F	5.0%	Clearing point [°C]:	79.0
PGU-2-F	4.0%	Δn [589 nm, 20°C]:	0.1047
CC-3-V1	12.0%	Δε [1 kHz, 20°C]:	5.3
CCP-V-1	14.0%	γ ₁ [mPa·s, 20°C]:	65
CCG-V-F	5.0%	V ₁₀ [V]:	1.72
CCP-30CF3	6.0%	V ₅₀ [V]:	2.07
CCZU-3-F	12.0%	V ₉₀ [V]:	2.57
PCH-301	9.0%	V ₉₀ /V ₁₀ :	1.496
CC-4-V	18.0%		
PUQU-2-F	3.0%		
PUQU-3-F	4.0%		
PGP-2-4	8.0%		

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Example 20

CCZU-2-F	4.0%	Clearing point [°C]:	78.0
CCZU-3-F	14.0%	Δn [589 nm, 20°C]:	0.0992
PUQU-1-F	8.0%	Δε [1 kHz, 20°C]:	5.8
PUQU-2-F	6.0%	γ ₁ [mPa·s, 20°C]:	66
CCP-V-1	13.0%	V ₁₀ [V]:	1.67
CCG-V-F	7.0%	V ₅₀ [V]:	2.00
CC-3-V1	15.0%	V ₉₀ [V]:	2.47
CC-4-V	18.0%	V ₉₀ /V ₁₀ :	1.480
PCH-301	5.0%		
PGP-2-3	4.0%		
PGP-2-4	6.0%		

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Example 21

CCP-20CF3	4.0%	Clearing point [°C]:	76.0
CCP-30CF3	4.0%	$\Delta\epsilon$ [1 kHz, 20°C]:	5.4
CCZU-3-F	4.0%	γ_1 [mPa·s, 20°C]:	58
PUQU-1-F	8.0%		
PUQU-2-F	8.0%		
CC-3-V1	6.0%		
CVCP-1V-OT	14.0%		
CVCP-2V-OT	4.0%		
PGP-2-4	8.0%		
CC-V-V1	40.0%		

Comparative Example 1

CCP-2F.F.F	9.5%	Clearing point [°C]:	80.0
CCP-3F.F.F	1.5%	Δn [589 nm, 20°C]:	0.0773
CCZU-2-F	3.5%	$\Delta\epsilon$ [1 kHz, 20°C]:	6.0
CCZU-3-F	9.0%	γ_1 [mPa·s, 20°C]:	81
CCP-20CF ₃	6.0%	V ₁₀ [V]:	1.60
CCP-30CF ₃	4.0%	V ₅₀ [V]:	1.97
CC-5-V	20.0%	V ₉₀ [V]:	2.45
CC-3-V1	5.0%	V ₉₀ /V ₁₀ :	1.526
PCH-301	6.0%		
CGZP-2-OT	9.0%		
CCP-V-1	4.0%		
CCG-V-F	10.5%		
CGU-2-F	5.0%		
CCH-35	3.5%		
CCP-20CF ₃ .F	3.5%		

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Example 22

5 10	PGP-2-3	6.0%	Clearing point [°C]:	75.0
	PGP-2-4	6.0%	Δn [589 nm, 20°C]:	0.1763
	PGP-3-3	6.0%	Δε [1 kHz, 20°C]:	4.5
	PCH-301	11.0%	γ ₁ [mPa·s, 20°C]:	150
	PCH-302	10.0%	V ₀ [V]:	1.66
	PGIGI-3-F	8.0%	γ ₁ /(Δn) ² :	4826
	GGP-2-F	10.0%	K ₁ [pN]:	11.3
	GGP-3-F	11.0%	K ₃ [pN]:	14.4
	GGP-5-F	10.0%	K ₃ / K ₁ :	1.27
	CCP-V-1	8.0%		
	CGG-3-F	14.0%		

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Example 23

20 25	PGP-2-3	6.0%	Clearing point [°C]:	77.0
	PGP-2-4	8.0%	Δn [589 nm, 20°C]:	0.1695
	PGP-3-3	6.0%	Δε [1 kHz, 20°C]:	4.4
	PCH-301	15.0%	γ ₁ [mPa·s, 20°C]:	156
	PCH-302	14.0%	V ₀ [V]:	1.73
	GGP-2-F	9.0%	γ ₁ /(Δn) ² :	5430
	GGP-3-F	9.0%	K ₁ [pN]:	11.7
	GGP-5-F	9.0%	K ₃ [pN]:	14.2
	CGG-3-F	18.0%	K ₃ / K ₁ :	1.21
	CBC-33F	3.0%		
	CBC-53F	3.0%		

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Example 24

5 10	PGP-2-3	10.0%	Clearing point [°C]:	79.0
	PGP-2-4	10.0%	Δn [589 nm, 20°C]:	0.1780
	PGP-3-3	6.0%	$\Delta \epsilon$ [1 kHz, 20°C]:	4.6
	PCH-301	13.0%	γ_1 [mPa·s, 20°C]:	153
	PCH-302	12.0%	V_0 [V]:	1.69
	GGP-2-F	9.0%	$\gamma_1/(\Delta n)^2$:	4829
	GGP-3-F	10.0%	K_1 [pN]:	11.8
	GGP-5-F	7.0%	K_3 [pN]:	14.0
	CGG-3-F	19.0%	K_3 / K_1 :	1.19
	CBC-33F	4.0%		

Example 25

15 20 25	PGP-2-3	11.0%	Clearing point [°C]:	80.5
	PGP-2-4	11.0%	Δn [589 nm, 20°C]:	0.1813
	PGP-3-2	6.0%	$\Delta \epsilon$ [1 kHz, 20°C]:	4.6
	PCH-301	12.0%	γ_1 [mPa·s, 20°C]:	157
	PCH-302	11.0%	V_0 [V]:	1.69
	GGP-2-F	9.0%	$\gamma_1/(\Delta n)^2$:	4776
	GGP-3-F	10.0%	K_1 [pN]:	11.9
	GGP-5-F	7.0%	K_3 [pN]:	13.7
	CGG-3-F	19.0%	K_3 / K_1 :	1.16
	CBC-33F	4.0%		

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Example 26

5 10	PGP-2-3	12.0%	Clearing point [°C]:	81.5
	PGP-2-4	12.0%	Δn [589 nm, 20°C]:	0.1885
	PGP-3-2	9.0%	$\Delta \epsilon$ [1 kHz, 20°C]:	4.7
	PCH-301	11.0%	γ_1 [mPa·s, 20°C]:	157
	PCH-302	9.0%	V_0 [V]:	1.70
	GGP-2-F	9.0%	$\gamma_1/(\Delta n)^2$:	4419
	GGP-3-F	10.0%	K_1 [pN]:	12.3
	GGP-5-F	6.0%		
	CGG-3-F	20.0%		
	CBC-33F	2.0%		

Example 27

15 20 25	PGP-2-3	13.0%	Clearing point [°C]:	80.0
	PGP-2-4	14.0%	Δn [589 nm, 20°C]:	0.1931
	PGP-3-2	9.0%	$\Delta \epsilon$ [1 kHz, 20°C]:	4.8
	PCH-301	12.0%	γ_1 [mPa·s, 20°C]:	152
	PCH-302	6.0%	V_0 [V]:	1.66
	GGP-2-F	9.0%	$\gamma_1/(\Delta n)^2$:	4076
	GGP-3-F	11.0%	K_1 [pN]:	12.3
	GGP-5-F	6.0%	K_3 [pN]:	12.7
	CGG-3-F	20.0%	K_3 / K_1 :	1.04

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Example 28

PGP-2-3	14.0%	Clearing point [°C]:	80.5
PGP-2-4	15.0%	Δn [589 nm, 20°C]:	0.1939
PGP-3-2	9.0%	Δε [1 kHz, 20°C]:	4.8
PCH-301	17.0%	γ ₁ [mPa·s, 20°C]:	157
GGP-2-F	9.0%	V ₀ [V]:	1.66
GGP-3-F	10.0%	γ ₁ /(Δn) ² :	4176
GGP-5-F	6.0%	K ₁ [pN]:	11.8
CGG-3-F	20.0%	K ₃ [pN]:	12.5
		K ₃ / K ₁ :	1.06

Example 29

PGP-2-3	15.0%	Clearing point [°C]:	84.5
PGP-2-4	15.0%	Δn [589 nm, 20°C]:	0.2001
PGP-3-2	9.0%	Δε [1 kHz, 20°C]:	5.3
PCH-301	13.0%	γ ₁ [mPa·s, 20°C]:	172
GGP-2-F	10.0%	V ₀ [V]:	1.64
GGP-3-F	10.0%	γ ₁ /(Δn) ² :	4296
GGP-5-F	7.0%	K ₁ [pN]:	12.4
CGG-3-F	21.0%	K ₃ [pN]:	12.2
		K ₃ / K ₁ :	0.98

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Example 30

5 10	PGP-2-3	15.0%	Clearing point [°C]:	83.0
	PGP-2-4	15.0%	Δn [589 nm, 20°C]:	0.2015
	PGP-3-2	9.0%	Δε [1 kHz, 20°C]:	5.0
	PCH-301	12.0%	γ ₁ [mPa·s, 20°C]:	159
	GGP-2-F	9.0%	V ₀ [V]:	1.72
	GGP-3-F	10.0%	γ ₁ /(Δn) ² :	3916
	GGP-5-F	6.0%	K ₁ [pN]:	13.1
	CGG-3-F	20.0%	K ₃ [pN]:	13.0
	PP-1-2V1	4.0%	K ₃ / K ₁ :	0.99

Example 31

15 20	PGP-2-3	16.0%	Clearing point [°C]:	87.5
	PGP-2-4	16.0%	Δn [589 nm, 20°C]:	0.2113
	PGP-3-2	11.0%	Δε [1 kHz, 20°C]:	4.8
	PCH-301	9.0%	γ ₁ [mPa·s, 20°C]:	174
	GGP-2-F	9.0%	V ₀ [V]:	1.83
	GGP-3-F	10.0%	γ ₁ /(Δn) ² :	3897
	GGP-5-F	6.0%	K ₁ [pN]:	14.5
	CGG-3-F	18.0%	K ₃ [pN]:	13.6
	PP-1-2V1	5.0%	K ₃ / K ₁ :	0.94

Comparative Example 2

25 30 35	FET-2Cl	15.0%	Clearing point [°C]:	80.3
	FET-3Cl	6.0%	Δn [589 nm, 20°C]:	0.2106
	FET-5Cl	19.0%	Δε [1 kHz, 20°C]:	5.5
	PGIGI-3-Cl	10.0%	γ ₁ [mPa·s, 20°C]:	299
	PGIGI-5-Cl	13.0%	V ₀ [V]:	1.76
	PCH-301	10.0%	γ ₁ /(Δn) ² :	6741
	GGP-5-Cl	16.0%	K ₁ [pN]:	14.4
	BCH-3F.F	11.0%	K ₃ [pN]:	19.6
			K ₃ / K ₁ :	1.36

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Example 32

PGU-1-F	5.00%	Clearing point [°C]:	79.0
PGU-2-F	4.00%	Δn [589 nm, 20°C]:	0.1047
CC-3-V1	12.00%	Δε [1 kHz, 20°C]:	5.3
CCP-V-1	14.00%	γ ₁ [mPa·s, 20°C]:	64
CCG-V-F	5.00%	V ₁₀ [V]:	1.75
CCP-30CF ₃	6.00%	V ₅₀ [V]:	2.11
CCZU-3-F	12.00%	V ₉₀ [V]:	2.62
PCH-301	9.00%	V ₉₀ /V ₁₀ :	1.499
CC-4-V	18.00%		
PUQU-2-F	7.00%		
PGP-2-4	8.00%		

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Example 33

CCP-20CF ₃	2.00%	Clearing point [°C]:	79.0
CCP-30CF ₃	8.00%	Δn [589 nm, 20°C]:	0.0930
CCZU-3-F	13.00%	Δε [1 kHz, 20°C]:	5.9
CC-3-V1	10.00%	γ ₁ [mPa·s, 20°C]:	67
PCH-301	8.00%	V ₁₀ [V]:	1.50
CCP-V-1	12.00%	V ₅₀ [V]:	1.65
CCG-V-F	10.00%	V ₉₀ [V]:	2.00
CC-4-V	18.00%	V ₉₀ /V ₁₀ :	1.511
PUQU-1-F	8.00%	K ₁ [pN]:	11.8
PUQU-2-F	6.00%	K ₃ [pN]:	13.5
PGP-2-3	5.00%	K ₃ / K ₁ :	1.15

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Example 34

5 10	PGU-1-F	3.00%	Clearing point [°C]:	81.0
	PGU-2-F	5.00%	Δn [589 nm, 20°C]:	0.1044
	CC-3-V1	11.00%	Δε [1 kHz, 20°C]:	5.5
	CCP-V-1	14.00%	γ ₁ [mPa·s, 20°C]:	65
	CCG-V-F	8.00%	V ₁₀ [V]:	1.70
	CCP-30CF ₃	6.00%	V ₅₀ [V]:	2.06
	CCZU-3-F	12.00%	V ₉₀ [V]:	2.55
	PCH-301	7.00%	V ₉₀ /V ₁₀ :	1.500
	CC-4-V	18.00%		
	PUQU-2-F	4.00%		
	PUQU-3-F	4.00%		
	PGP-2-4	8.00%		

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Example 35

20 25	CCP-20CF ₃	4.00%	Clearing point [°C]:	79.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1024
	CCZU-3-F	4.00%	Δε [1 kHz, 20°C]:	6.1
	PUQU-1-F	9.00%	γ ₁ [mPa·s, 20°C]:	75
	PUQU-2-F	7.00%	V ₁₀ [V]:	1.76
	CC-3-V1	12.00%	V ₅₀ [V]:	2.14
	CVCP-1V-OT	14.00%	V ₉₀ [V]:	2.66
	CVCP-2V-OT	6.00%	V ₉₀ /V ₁₀ :	1.511
	PGP-2-3	4.00%		
	PGP-2-4	6.00%		
	CC-V2-V	30.00%		

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Example 36

5	CC-4-V	18.00%	Clearing point [°C]:	74.5
	CCP-1F.F.F.F	2.50%	Δn [589 nm, 20°C]:	0.0893
	CCQU-2-F	14.00%	Δε [1 kHz, 20°C]:	12.8
	CCQU-3-F	13.00%	γ ₁ [mPa·s, 20°C]:	103
	CCQU-5-F	11.00%	V ₁₀ [V]:	1.10
	CCQG-3-F	8.00%	V ₅₀ [V]:	1.35
	CCP-30CF ₃	3.00%	V ₉₀ [V]:	1.69
	PUQU-1-F	8.00%	V ₉₀ /V ₁₀ :	1.539
	PUQU-2-F	5.00%		
	PUQU-3-F	9.00%		
10	PGP-2-4	3.00%		
	CCGU-3-F	3.50%		
	CBC-33	2.00%		
15.				

Example 37

20	CC-4-V	14.00%	Clearing point [°C]:	82.0
	CC-3-V1	8.00%	Δn [589 nm, 20°C]:	0.0918
	CCQU-2-F	14.00%	Δε [1 kHz, 20°C]:	12.0
	CCQU-3-F	12.00%	γ ₁ [mPa·s, 20°C]:	106
	CCQU-5-F	10.00%	V ₁₀ [V]:	1.22
	CCP-2F.F.F	4.00%	V ₅₀ [V]:	1.50
	CCP-30CF ₃	8.00%	V ₉₀ [V]:	1.87
	PUQU-1-F	8.00%	V ₉₀ /V ₁₀ :	1.535
	PUQU-2-F	4.00%		
	PUQU-3-F	7.00%		
25	PGP-2-4	3.00%		
	CCGU-3-F	6.00%		
	CBC-33	2.00%		
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Example 38

5	CC-4-V	18.00%	Clearing point [°C]:	74.5
	CCP-1F.F.F	6.00%	Δn [589 nm, 20°C]:	0.0890
	CCQU-2-F	14.00%	Δε [1 kHz, 20°C]:	12.6
10	CCQU-3-F	13.00%	γ ₁ [mPa·s, 20°C]:	107
	CCQU-5-F	12.00%	V ₁₀ [V]:	1.10
	CCQG-3-F	8.00%	V ₅₀ [V]:	1.36
	PUQU-1-F	7.00%	V ₉₀ [V]:	1.71
15	PUQU-2-F	4.00%	V ₉₀ /V ₁₀ :	1.550
	PUQU-3-F	7.00%		
	PGP-2-3	4.00%		
	CCGU-3-F	7.00%		

Example 39

20	CC-4-V	14.00%	Clearing point [°C]:	81.0
	CC-3-V1	8.00%	Δn [589 nm, 20°C]:	0.0911
	CCQU-2-F	13.00%	Δε [1 kHz, 20°C]:	11.5
25	CCQU-3-F	13.00%	γ ₁ [mPa·s, 20°C]:	108
	CCQU-5-F	10.00%	V ₁₀ [V]:	1.24
	CCP-1F.F.F	5.00%	V ₅₀ [V]:	1.53
	CCQG-3-F	2.00%	V ₉₀ [V]:	1.91
30	CCP-30CF ₃	8.00%	V ₉₀ /V ₁₀ :	1.536
	PUQU-1-F	7.00%		
	PUQU-2-F	3.00%		
	PUQU-3-F	6.00%		
	PGP-2-3	4.00%		
	CCGU-3-F	7.00%		

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Example 40

5 10 15	PGU-1-F	8.00%	Clearing point [°C]:	80.0
	CC-3-V1	12.00%	Δn [589 nm, 20°C]:	0.1043
	CCP-V-1	14.00%	Δε [1 kHz, 20°C]:	5.4
	CCG-V-F	5.00%	V ₁₀ [V]:	1.77
	CCP-30CF ₃	6.00%	V ₅₀ [V]:	2.13
	CCZU-3-F	13.00%	V ₉₀ [V]:	2.65
	PCH-301	10.00%	V ₉₀ /V ₁₀ :	1.494
	CC-4-V	17.00%	K ₁ [pN]:	12.3
	PUQU-2-F	3.00%	K ₃ [pN]:	12.9
	PUQU-3-F	4.00%	K ₃ / K ₁ :	1.05
	PGP-2-4	8.00%		

Example 41

20 25 30	CC-4-V	14.00%	Clearing point [°C]:	81.0
	CC-3-V1	8.00%	Δn [589 nm, 20°C]:	0.0921
	CCQU-2-F	13.00%	Δε [1 kHz, 20°C]:	11.4
	CCQU-3-F	12.00%	γ ₁ [mPa·s, 20°C]:	100
	CCQU-5-F	11.00%	V ₁₀ [V]:	1.25
	CCP-1F.F.F	4.00%	V ₅₀ [V]:	1.53
	BCH-3F.F.F	3.00%	V ₉₀ [V]:	1.90
	CCP-30CF ₃	8.00%	V ₉₀ /V ₁₀ :	1.522
	PUQU-1-F	9.00%		
	PUQU-2-F	7.00%		
	PGP-2-3	4.00%		
	CCGU-3-F	6.00%		
	CBC-33	1.00%		

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Example 42

5 10	CC-4-V	14.00%	Clearing point [°C]:	76.0
	CCQU-2-F	13.00%	Δn [589 nm, 20°C]:	0.0878
	CCQU-3-F	13.00%	Δε [1 kHz, 20°C]:	12.5
	CCQU-5-F	11.00%	γ ₁ [mPa·s, 20°C]:	111
	CCP-1F.F.F	8.00%	V ₁₀ [V]:	1.10
	CCQG-3-F	8.00%	V ₅₀ [V]:	1.36
	CCP-20CF ₃	6.00%	V ₉₀ [V]:	1.69
	PUQU-2-F	7.00%	V ₉₀ /V ₁₀ :	1.537
	PUQU-3-F	10.00%		
	PGP-2-3	3.00%		
	CCGU-3-F	7.00%		

15 Example 43

20 25	CC-4-V	18.00%	Clearing point [°C]:	74.0
	CCP-1F.F.F	7.00%	Δn [589 nm, 20°C]:	0.0887
	CCP-2F.F.F	2.00%	Δε [1 kHz, 20°C]:	11.9
	CCQU-2-F	14.00%	γ ₁ [mPa·s, 20°C]:	103
	CCQU-3-F	13.00%	V ₁₀ [V]:	1.11
	CCQU-5-F	11.00%	V ₅₀ [V]:	1.37
	CCQG-3-F	8.00%	V ₉₀ [V]:	1.72
	PUQU-1-F	9.00%	V ₉₀ /V ₁₀ :	1.545
	PUQU-2-F	7.00%		
	PGP-2-3	5.00%		
	CCGU-3-F	6.00%		

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Example 44

5	CC-4-V	12.00%	Clearing point [°C]:	81.5
	CC-3-V1	7.00%	Δn [589 nm, 20°C]:	0.0938
	CCQU-2-F	13.00%	Δε [1 kHz, 20°C]:	11.8
	CCQU-3-F	12.00%	γ ₁ [mPa·s, 20°C]:	111
	CCQU-5-F	11.00%	V ₁₀ [V]:	1.22
	CCP-1F.F.F	5.00%	V ₅₀ [V]:	1.50
	CCP-2F.F.F	4.00%	V ₉₀ [V]:	1.87
	CCP-30CF ₃	8.00%	V ₉₀ /V ₁₀ :	1.533
	PUQU-1-F	9.00%		
	PUQU-3-F	7.00%		
10	PGP-2-3	5.00%		
	CCGU-3-F	6.00%		
	CBC-33	1.00%		
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Example 45

20	CCP-20CF ₃	2.00%	Clearing point [°C]:	79.5
	CCP-30CF ₃	8.00%	Δn [589 nm, 20°C]:	0.0948
	CCZU-3-F	13.00%	Δε [1 kHz, 20°C]:	5.9
	CC-3-V1	10.00%	γ ₁ [mPa·s, 20°C]:	64
	PCH-301	7.00%	V ₁₀ [V]:	1.64
	CCP-V-1	12.00%	V ₅₀ [V]:	1.99
	CCG-V-F	10.00%	V ₉₀ [V]:	2.48
	CC-4-V	18.00%	V ₉₀ /V ₁₀ :	1.513
	PUQU-1-F	8.00%	K ₁ [pN]:	11.7
	PUQU-2-F	6.00%	K ₃ [pN]:	13.4
25	PGP-2-2	6.00%	K ₃ / K ₁ :	1.15
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Example 46

5 10	CCP-20CF ₃	2.00%	Clearing point [°C]:	79.5
	CCP-30CF ₃	8.00%	Δn [589 nm, 20°C]:	0.0939
	CCZU-3-F	13.00%	Δε [1 kHz, 20°C]:	6.0
	CC-3-V1	10.00%	γ ₁ [mPa·s, 20°C]:	69
	PCH-301	7.00%	V ₁₀ [V]:	1.66
	CCP-V-1	12.00%	V ₅₀ [V]:	2.01
	CCG-V-F	10.00%	V ₉₀ [V]:	2.49
	CC-4-V	18.00%	V ₉₀ /V ₁₀ :	1.497
	PUQU-1-F	8.00%	K ₁ [pN]:	11.8
	PUQU-2-F	6.00%	K ₃ [pN]:	13.3
	PGP-2-4	6.00%	K ₃ / K ₁ :	1.13

15 Example 47

20 25	CCP-20CF ₃	3.00%	Clearing point [°C]:	78.0
	CCP-30CF ₃	7.00%	Δn [589 nm, 20°C]:	0.0996
	CCZU-3-F	13.00%	Δε [1 kHz, 20°C]:	5.7
	CC-3-V1	12.00%	γ ₁ [mPa·s, 20°C]:	63
	PCH-301	7.00%	V ₁₀ [V]:	1.68
	CCP-V-1	10.00%	V ₅₀ [V]:	2.02
	CCG-V-F	6.00%	V ₉₀ [V]:	2.49
	CC-4-V	18.00%	V ₉₀ /V ₁₀ :	1.479
	PUQU-1-F	8.00%	K ₁ [pN]:	12.1
	PUQU-2-F	6.00%	K ₃ [pN]:	12.5
	PGP-2-4	6.00%	K ₃ / K ₁ :	1.03
	PGP-2-2	4.00%		

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Example 48

CCP-30CF ₃	4.00%	Clearing point [°C]:	76.5
CCZU-3-F	10.00%	Δn [589 nm, 20°C]:	0.1090
CCP-V-1	11.00%	Δε [1 kHz, 20°C]:	6.3
CCG-V-F	8.00%	γ ₁ [mPa·s, 20°C]:	66
CC-4-V	18.00%	V ₁₀ [V]:	1.65
CC-3-V1	13.00%	V ₅₀ [V]:	1.96
PCH-301	4.00%	V ₉₀ [V]:	2.41
PUQU-1-F	8.00%	V ₉₀ /V ₁₀ :	1.458
PUQU-2-F	4.00%	K ₁ [pN]:	12.3
PUQU-3-F	6.00%	K ₃ [pN]:	12.1
PGP-2-3	7.00%	K ₃ / K ₁ :	0.99
PGP-2-4	7.00%		

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Example 49

CCZU-3-F	12.00%	Clearing point [°C]:	80.0
CCP-V-1	8.00%	Δn [589 nm, 20°C]:	0.1011
CCG-V-F	10.00%	Δε [1 kHz, 20°C]:	6.2
CC-3-V1	13.00%	γ ₁ [mPa·s, 20°C]:	67
CC-4-V	18.00%	V ₁₀ [V]:	1.64
PCH-301	5.00%	V ₅₀ [V]:	1.97
PUQU-1-F	8.00%	V ₉₀ [V]:	2.45
PUQU-2-F	4.00%	V ₉₀ /V ₁₀ :	1.491
PUQU-3-F	6.00%	K ₁ [pN]:	11.9
PGP-2-3	4.00%	K ₃ [pN]:	12.6
PGP-2-4	6.00%	K ₃ / K ₁ :	1.06
CVCC-V-2	3.00%		
CVCC-V-3	3.00%		

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Example 50

CCZU-3-F	12.00%	Clearing point [°C]:	77.0
CCP-V-1	10.00%	Δn [589 nm, 20°C]:	0.1092
CCG-V-F	9.00%	Δε [1 kHz, 20°C]:	6.3
CC-4-V	10.00%	γ ₁ [mPa·s, 20°C]:	66
CC-3-V1	13.00%	V ₁₀ [V]:	1.65
PCH-301	4.00%	V ₅₀ [V]:	1.97
PUQU-1-F	8.00%	V ₉₀ [V]:	2.42
PUQU-2-F	4.00%	V ₉₀ /V ₁₀ :	1.458
PUQU-3-F	6.00%	K ₁ [pN]:	12.8
PGP-2-3	7.00%	K ₃ [pN]:	12.5
PGP-2-4	7.00%	K ₃ / K ₁ :	0.98
CC-3-2V	10.00%		

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Example 51

PGP-2-3	14.00%	Clearing point [°C]:	78.5
PGP-2-4	15.00%	Δn [589 nm, 20°C]:	0.1911
PGP-3-2	9.00%	Δε [1 kHz, 20°C]:	4.5
PCH-301	19.00%	γ ₁ [mPa·s, 20°C]:	149
GGP-2-F	10.00%		
GGP-3-F	10.00%		
GGP-5-F	4.00%		
CGG-3-F	19.00%		

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Example 52

PGP-2-3	15.00%	Clearing point [°C]:	76.0
PGP-2-4	15.00%	Δn [589 nm, 20°C]:	0.1888
PGP-3-2	9.00%	Δε [1 kHz, 20°C]:	5.2
PCH-301	19.00%	γ ₁ [mPa·s, 20°C]:	149
CGG-3-F	18.00%		
GGG-3-F	8.00%		
GGG-5-F	8.00%		
GGP-3-F	8.00%		

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Example 53

CCP-1F.F.F	8.00%	Clearing point [°C]:	76.5
CCP-3F.F.F	5.00%	Δn [589 nm, 20°C]:	0.1045
CCP-20CF ₃	6.00%	Δε [1 kHz, 20°C]:	8.1
CCP-30CF ₃	7.00%	γ ₁ [mPa·s, 20°C]:	69
PGU-2-F	6.00%	K ₁ [pN]:	12.4
PUQU-2-F	9.00%	K ₃ [pN]:	12.5
PUQU-3-F	9.00%	K ₃ / K ₁ :	1.00
CCP-V-1	9.00%		
CCP-V2-1	7.00%		
CC-3-V1	13.00%		
CC-4-V	15.00%		
PGP-2-3	6.00%		

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Example 54

5 10	CCP-1F.F.F	8.00%	Clearing point [°C]:	74.5
	CCP-3F.F.F	10.00%	Δn [589 nm, 20°C]:	0.1046
	CCP-20CF ₃	6.00%	Δε [1 kHz, 20°C]:	7.9
	CCP-30CF ₃	7.00%	γ ₁ [mPa·s, 20°C]:	72
	PUQU-2-F	10.00%	K ₁ [pN]:	14.9
	PUQU-3-F	10.00%	K ₃ [pN]:	13.7
	CCP-V-1	10.00%	K ₃ / K ₁ :	0.92
	CCP-V2-1	3.00%		
	CC-3-V1	12.00%		
	CC-5-V	13.00%		
	PGP-2-3	5.50%		
	PP-1-2V1	5.50%		

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Example 55

20 25	PGU-1-F	9.00%	Clearing point [°C]:	80.0
	CC-3-V1	12.00%	Δn [589 nm, 20°C]:	0.1029
	CCP-V-1	14.00%	Δε [1 kHz, 20°C]:	5.0
	CCG-V-F	5.00%	K ₁ [pN]:	12.4
	CCP-30CF ₃	6.00%	K ₃ [pN]:	13.1
	CCZU-3-F	12.00%	K ₃ / K ₁ :	1.05
	PCH-301	9.00%		
	CC-4-V	18.00%		
	PUQU-2-F	7.00%		
	PGP-2-4	8.00%		

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Example 56

5 10	PGIGI-3-F	10.00%	Clearing point [°C]:	80.0
	PP-1-2V1	10.00%	Δn [589 nm, 20°C]:	0.2024
	PCH-301	19.00%	$\Delta \epsilon$ [1 kHz, 20°C]:	6.1
	PGP-2-3	14.00%	γ_1 [mPa·s, 20°C]:	178
	PGP-2-4	14.00%	K_1 [pN]:	18.6
	PGU-2-F	9.00%	K_3 [pN]:	25.1
	PGU-3-F	9.00%	K_3 / K_1 :	1.35
	PGU-5-F	8.00%		
	CBC-33F	4.00%		
	CBC-53F	3.00%		

Example 57

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20 25	CC-4-V	18.00%	Clearing point [°C]:	82.5
	CC-3-V1	7.00%	Δn [589 nm, 20°C]:	0.0944
	CCP-20CF ₃	8.00%	$\Delta \epsilon$ [1 kHz, 20°C]:	11.3
	BCH-3F.F.F	5.00%	γ_1 [mPa·s, 20°C]:	102
	CCZU-3-F	14.00%	V_{10} [V]:	1.22
	PUQU-2-F	7.00%	V_{50} [V]:	1.51
	PUQU-3-F	10.00%	V_{90} [V]:	1.86
	CCQU-2-F	6.00%	V_{90}/V_{10} :	1.531
	CCQU-3-F	13.00%		
	PGP-2-3	3.00%		
	CCGU-3-F	7.00%		
	CBC-33	2.00%		

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Example 58

CC-4-V	12.00%	Clearing point [°C]:	76.0
CCQU-2-F	13.00%	Δn [589 nm, 20°C]:	0.0889
CCQU-3-F	14.00%	Δε [1 kHz, 20°C]:	11.6
CCQU-5-F	11.00%	γ ₁ [mPa·s, 20°C]:	119
CCP-1F.F.F	6.00%	V ₁₀ [V]:	1.14
CCP-2F.F.F	5.00%	V ₅₀ [V]:	1.40
CCQG-2-F	7.00%	V ₉₀ [V]:	1.76
CCP-20CF ₃	5.00%	V ₉₀ /V ₁₀ :	1.540
PUQG-2-F	9.00%		
PUQG-3-F	8.00%		
PGP-2-3	3.00%		
CCGU-3-F	7.00%		

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Example 59

CCP-2F.F.F	8.00%	Clearing point [°C]:	73.0
CCP-3F.F.F	5.00%	Δn [589 nm, 20°C]:	0.1099
PGU-1-F	5.00%	Δε [1 kHz, 20°C]:	4.5
PUQU-1-F	6.00%	γ ₁ [mPa·s, 20°C]:	61
PUQU-3-F	4.00%	V ₁₀ [V]:	1.86
CC-3-V1	13.00%	V ₅₀ [V]:	2.22
CC-4-V	18.00%	V ₉₀ [V]:	2.74
CCP-V-1	14.00%	V ₉₀ /V ₁₀ :	1.474
CCP-V2-1	3.00%	K ₁ [pN]:	11.8
PCH-301	10.00%	K ₃ [pN]:	11.8
PGP-2-3	6.00%	K ₃ / K ₁ :	1.00
PGP-2-4	8.00%		

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Example 60

5	CCP-20CF ₃	4.00%	Clearing point [°C]:	78.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.0987
	CCZU-3-F	12.00%	Δε [1 kHz, 20°C]:	5.6
	CCP-V-1	13.00%	γ ₁ [mPa·s, 20°C]:	64
	CCP-V2-1	4.00%	V ₁₀ [V]:	1.74
	CC-4-V	18.00%	V ₅₀ [V]:	2.09
	CC-3-V1	13.00%	V ₉₀ [V]:	2.57
	PCH-301	8.00%	V ₉₀ /V ₁₀ :	1.477
	PUQU-1-F	6.00%	K ₁ [pN]:	12.5
	PUQU-2-F	4.00%	K ₃ [pN]:	12.9
10	PUQU-3-F	6.00%	K ₃ / K ₁ :	1.03
	PGP-2-2	4.00%		
	PGP-2-4	4.00%		
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Example 61

20	CCP-20CF ₃	4.00%	Clearing point [°C]:	82.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1045
	CCQU-2-F	5.00%	Δε [1 kHz, 20°C]:	5.6
	CCQU-3-F	12.00%	γ ₁ [mPa·s, 20°C]:	76
	CCQU-5-F	5.00%	V ₁₀ [V]:	1.79
	CC-3-V1	16.00%	V ₅₀ [V]:	2.14
	CC-4-V	12.00%	V ₉₀ [V]:	2.64
	CVCP-1V-OT	16.00%	V ₉₀ /V ₁₀ :	1.479
	PGP-2-2V	7.00%	K ₁ [pN]:	12.9
	PGP-2-4	7.00%	K ₃ [pN]:	13.5
25	GU-1V2-F	12.00%	K ₃ / K ₁ :	1.05
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Example 62

5	CCP-20CF ₃	4.00%	Clearing point [°C]:	78.5
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.0990
	CCZU-3-F	12.00%	Δε [1 kHz, 20°C]:	5.6
	CCP-V-1	13.00%	γ ₁ [mPa·s, 20°C]:	65
	CCP-V2-1	4.00%	V ₁₀ [V]:	1.74
	CC-4-V	18.00%	V ₅₀ [V]:	2.09
	CC-3-V1	13.00%	V ₉₀ [V]:	2.60
	PCH-301	8.00%	V ₉₀ /V ₁₀ :	1.491
	PUQU-1-F	6.00%	K ₁ [pN]:	12.5
	PUQU-2-F	4.00%	K ₃ [pN]:	13.1
10	PUQU-3-F	6.00%	K ₃ / K ₁ :	1.05
	PGP-2-3	4.00%		
	PGP-2-4	4.00%		
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Example 63

20	CCP-20CF ₃	4.00%	Clearing point [°C]:	81.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.0982
	CCZU-3-F	12.00%	Δε [1 kHz, 20°C]:	6.3
	CCP-V-1	16.00%	γ ₁ [mPa·s, 20°C]:	67
	CCP-V2-1	4.00%	V ₁₀ [V]:	1.70
	CC-4-V	18.00%	V ₅₀ [V]:	2.04
	CC-3-V1	13.00%	V ₉₀ [V]:	2.52
	PCH-301	5.00%	V ₉₀ /V ₁₀ :	1.487
	PUQU-2-F	8.00%	K ₁ [pN]:	12.6
	PUQU-3-F	8.00%	K ₃ [pN]:	13.7
25	PGP-2-F	4.00%	K ₃ / K ₁ :	1.09
	PGP-4-F	4.00%		
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Example 64

CCQG-2-F	5.00%	Clearing point [°C]:	79.5
CCQG-3-F	6.00%	Δn [589 nm, 20°C]:	0.1034
CCQU-2-F	10.00%	Δε [1 kHz, 20°C]:	6.0
CCQU-3-F	12.00%	γ ₁ [mPa·s, 20°C]:	78
CC-3-V1	16.00%	V ₁₀ [V]:	1.69
CC-4-V	9.00%	V ₅₀ [V]:	2.03
CVCP-1V-OT	16.00%	V ₉₀ [V]:	2.52
PGP-2-3	7.00%	V ₉₀ /V ₁₀ :	1.488
PGP-2-4	7.00%	K ₁ [pN]:	12.4
GU-1V2-F	12.00%	K ₃ [pN]:	12.9
		K ₃ / K ₁ :	1.04

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Example 65

CVCP-1V-OT	12.00%	Clearing point [°C]:	81.5
CCQU-2-F	12.00%	Δn [589 nm, 20°C]:	0.1004
CCQU-3-F	10.00%	Δε [1 kHz, 20°C]:	5.6
CCP-2F.F.F	11.00%	γ ₁ [mPa·s, 20°C]:	82
CCP-3F.F.F	12.00%	V ₁₀ [V]:	1.91
CC-3-V1	14.00%	V ₅₀ [V]:	2.29
CC-5-V	10.00%	V ₉₀ [V]:	2.83
PGP-2-4	6.00%	V ₉₀ /V ₁₀ :	1.483
PP-1-2V1	13.00%	K ₁ [pN]:	14.2
		K ₃ [pN]:	15.0
		K ₃ / K ₁ :	1.06

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Example 66

CCP-20CF ₃	3.50%	Clearing point [°C]:	79.5
CCP-30CF ₃	4.50%	Δn [589 nm, 20°C]:	0.0991
CCZU-3-F	12.00%	Δε [1 kHz, 20°C]:	5.6
CC-3-V1	13.00%	γ ₁ [mPa·s, 20°C]:	65
PCH-301	7.00%	V ₁₀ [V]:	1.73
CCP-V-1	13.00%	V ₅₀ [V]:	2.08
CCP-V2-1	5.00%	V ₉₀ [V]:	2.58
CC-4-V	18.00%	V ₉₀ /V ₁₀ :	1.491
PUQU-2-F	8.00%	K ₁ [pN]:	12.7
PUQU-3-F	8.00%	K ₃ [pN]:	13.1
PGP-2-4	8.00%	K ₃ / K ₁ :	1.03

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Example 67

CCZU-3-F	12.00%	Clearing point [°C]:	79.5
CC-3-V1	13.00%	Δn [589 nm, 20°C]:	0.1029
CC-4-V	18.00%	Δε [1 kHz, 20°C]:	7.8
PCH-301	8.00%	γ ₁ [mPa·s, 20°C]:	77
CCP-V-1	14.00%	V ₁₀ [V]:	1.53
PUQU-2-F	6.00%	V ₅₀ [V]:	1.84
PUQU-3-F	6.00%	V ₉₀ [V]:	2.28
CDUQU-2-F	6.00%	V ₉₀ /V ₁₀ :	1.490
CDUQU-4-F	6.00%	K ₁ [pN]:	12.6
PGP-2-3	6.00%	K ₃ [pN]:	12.7
PGP-2-4	5.00%	K ₃ / K ₁ :	1.00

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Example 68

5	BCH-3F.F.F	9.00%	Clearing point [°C]:	71.5
	BCH-5F.F.F	6.00%	Δn [589 nm, 20°C]:	0.1134
	PUQU-1-F	7.00%	Δε [1 kHz, 20°C]:	8.4
	PUQU-2-F	8.00%	γ ₁ [mPa·s, 20°C]:	74
	PUQU-3-F	5.00%	V ₁₀ [V]:	1.40
	CC-3-V1	12.00%	V ₅₀ [V]:	1.69
	CC-5-V	10.00%	V ₉₀ [V]:	2.09
10	CCP-V-1	14.00%	V ₉₀ /V ₁₀ :	1.493
	PCH-301	7.00%	K ₁ [pN]:	11.7
	PGP-2-4	10.00%	K ₃ [pN]:	11.4
	CCQU-3-F	7.00%	K ₃ / K ₁ :	0.97
	CCQU-5-F	5.00%		

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Example 69

20	CCP-20CF ₃	2.00%	Clearing point [°C]:	80.0
	CCP-30CF ₃	8.00%	Δn [589 nm, 20°C]:	0.0950
	CCZU-3-F	13.00%	Δε [1 kHz, 20°C]:	6.0
	CC-3-V1	10.00%	γ ₁ [mPa·s, 20°C]:	67
	PCH-301	7.00%	V ₁₀ [V]:	1.67
	CCP-V-1	12.00%	V ₅₀ [V]:	2.03
	CCG-V-F	10.00%	V ₉₀ [V]:	2.56
25	CC-4-V	18.00%	V ₉₀ /V ₁₀ :	1.533
	PUQU-1-F	8.00%	K ₁ [pN]:	11.8
	PUQU-2-F	6.00%	K ₃ [pN]:	13.5
	PGP-2-3	6.00%	K ₃ / K ₁ :	1.14

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Example 70

5 10	CCP-20CF ₃	2.00%	Clearing point [°C]:	79.5
	CCP-30CF ₃	8.00%	Δn [589 nm, 20°C]:	0.0946
	CCZU-3-F	13.00%	Δε [1 kHz, 20°C]:	5.9
	CC-3-V1	10.00%	V ₁₀ [V]:	1.64
	PCH-301	7.00%	V ₅₀ [V]:	2.00
	CCP-V-1	12.00%	V ₉₀ [V]:	2.53
	CCG-V-F	10.00%	V ₉₀ /V ₁₀ :	1.543
	CC-4-V	18.00%	K ₁ [pN]:	11.7
	PUQU-1-F	8.00%	K ₃ [pN]:	13.4
	PUQU-2-F	6.00%	K ₃ / K ₁ :	1.15
	PGP-2-4	6.00%		

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Example 71

20 25	CCP-20CF ₃	2.00%	Clearing point [°C]:	81.0
	CCP-30CF ₃	8.00%	Δn [589 nm, 20°C]:	0.0951
	CCZU-3-F	13.00%	Δε [1 kHz, 20°C]:	6.0
	CC-3-V1	10.00%	γ ₁ [mPa·s, 20°C]:	67
	PCH-301	7.00%	V ₁₀ [V]:	1.67
	CCP-V-1	12.00%	V ₅₀ [V]:	2.03
	CCG-V-F	10.00%	V ₉₀ [V]:	2.56
	CC-4-V	18.00%	V ₉₀ /V ₁₀ :	1.533
	PUQU-1-F	8.00%	K ₁ [pN]:	11.8
	PUQU-2-F	6.00%	K ₃ [pN]:	13.9
	PGP-2-2V	6.00%	K ₃ / K ₁ :	1.18

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Example 72

CCP-20CF ₃	3.50%	Clearing point [°C]:	82.0
CCP-30CF ₃	4.50%	Δn [589 nm, 20°C]:	0.1000
CCZU-3-F	12.00%	Δε [1 kHz, 20°C]:	5.7
CCP-V-1	13.00%	γ ₁ [mPa·s, 20°C]:	66
CCP-V2-1	5.00%	V ₁₀ [V]:	1.76
CC-4-V	18.00%	V ₅₀ [V]:	2.11
CC-3-V1	13.00%	V ₉₀ [V]:	2.62
PCH-301	7.00%	V ₉₀ /V ₁₀ :	1.489
PUQU-2-F	8.00%	K ₁ [pN]:	12.9
PUQU-3-F	8.00%	K ₃ [pN]:	13.8
PGP-2-2V	8.00%	K ₃ / K ₁ :	1.07

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Example 73

CCP-20CF ₃	0.00%	Clearing point [°C]:	80.0
CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.0996
CCZU-3-F	12.00%	Δε [1 kHz, 20°C]:	6.5
CCP-V-1	13.00%	K ₁ [pN]:	11.9
CCP-V2-1	5.00%	K ₃ [pN]:	13.7
CC-4-V	15.00%	K ₃ / K ₁ :	1.15
CC-3-V1	13.00%		
PCH-301	6.00%		
PUQU-2-F	8.00%		
PUQU-3-F	8.00%		
PGP-2-F	5.00%		
PGP-4-F	3.00%		
CCG-V-F	8.00%		

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Example 74

5	CCP-20CF ₃	2.00%	Clearing point [°C]:	79.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.0992
	CCZU-3-F	10.00%	Δε [1 kHz, 20°C]:	6.4
	CCP-V-1	13.00%	K ₁ [pN]:	11.8
	CCP-V2-1	0.00%	K ₃ [pN]:	14.0
	CC-4-V	15.00%	K ₃ / K ₁ :	1.19
	CC-3-V1	13.00%		
	PCH-301	9.00%		
	PUQU-2-F	8.00%		
	PUQU-3-F	8.00%		
10	PGP-2-F	5.00%		
	PGP-4-F	3.00%		
	CVCP-1V-OT	10.00%		
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Example 75

20	CCP-2F.F.F	5.00%	Clearing point [°C]:	75.5
	CCP-3F.F.F	11.00%	Δn [589 nm, 20°C]:	0.1086
	PUQU-2-F	6.00%	Δε [1 kHz, 20°C]:	4.9
	PUQU-3-F	8.00%	γ ₁ [mPa·s, 20°C]:	67
	CC-3-V1	12.00%	V ₁₀ [V]:	1.83
	CC-4-V	14.00%	V ₅₀ [V]:	2.19
	CCP-V-1	11.00%	V ₉₀ [V]:	2.71
	CCP-V2-1	8.00%	V ₉₀ /V ₁₀ :	1.485
	PCH-301	11.00%	K ₁ [pN]:	12.0
	PGP-2-3	7.00%	K ₃ [pN]:	12.4
25	PGP-2-4	7.00%	K ₃ / K ₁ :	1.03
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Example 76

CCP-20CF ₃	4.00%	Clearing point [°C]:	75.5
CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1076
PGU-2-F	2.00%	Δε [1 kHz, 20°C]:	4.5
PGU-3-F	4.00%	γ ₁ [mPa·s, 20°C]:	61
PUQU-2-F	5.00%	V ₁₀ [V]:	1.86
PUQU-3-F	6.00%	V ₅₀ [V]:	2.23
CC-3-V1	12.00%	V ₉₀ [V]:	2.77
CC-4-V	16.00%	V ₉₀ /V ₁₀ :	1.493
CCP-V-1	15.00%	K ₁ [pN]:	11.6
CCG-V-F	12.00%	K ₃ [pN]:	12.5
PCH-301	10.00%	K ₃ / K ₁ :	1.08
PGP-2-3	5.00%		
PGP-2-4	5.00%		

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Example 77

CCP-30CF ₃	4.00%	Clearing point [°C]:	79.0
CCZU-2-F	3.00%	Δn [589 nm, 20°C]:	0.1007
CCZU-3-F	14.00%	Δε [1 kHz, 20°C]:	5.5
CC-3-V1	13.00%	γ ₁ [mPa·s, 20°C]:	66
CC-4-V	18.00%	V ₁₀ [V]:	1.75
PCH-301	8.00%	V ₅₀ [V]:	2.09
CCP-V-1	16.00%	V ₉₀ [V]:	2.59
PUQU-2-F	6.00%	V ₉₀ /V ₁₀ :	1.477
PUQU-3-F	8.00%	K ₁ [pN]:	12.4
PGP-2-3	5.00%	K ₃ [pN]:	12.7
PGP-2-4	5.00%	K ₃ / K ₁ :	1.02

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Example 78

5	CVCP-1V-OT	8.00%	Clearing point [°C]:	79.0
	CCZU-2-F	3.00%	Δn [589 nm, 20°C]:	0.1011
	CCZU-3-F	14.00%	Δε [1 kHz, 20°C]:	5.7
	CC-3-V1	13.00%	γ ₁ [mPa·s, 20°C]:	69
	CC-4-V	18.00%	V ₁₀ [V]:	1.69
	PCH-301	8.50%	V ₅₀ [V]:	2.03
	CCP-V-1	11.50%	V ₉₀ [V]:	2.50
	PUQU-2-F	6.00%	V ₉₀ /V ₁₀ :	1.481
	PUQU-3-F	8.00%	K ₁ [pN]:	12.0
	PGP-2-3	5.00%	K ₃ [pN]:	13.0
	PGP-2-4	5.00%	K ₃ / K ₁ :	1.08

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Example 79

20	CCP-20CF ₃	4.00%	Clearing point [°C]:	75.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1013
	PUQU-2-F	7.00%	Δε [1 kHz, 20°C]:	4.5
	PUQU-3-F	9.00%	γ ₁ [mPa·s, 20°C]:	65
	CCP-3F.F.F	5.00%	V ₁₀ [V]:	1.93
	CCP-V-1	11.00%	V ₅₀ [V]:	2.30
	CCP-V2-1	9.00%	V ₉₀ [V]:	2.85
	CC-5-V	15.00%	V ₉₀ /V ₁₀ :	1.478
	CC-3-V1	13.00%	K ₁ [pN]:	12.3
	PCH-301	15.00%	K ₃ [pN]:	13.6
	PGP-2-3	4.00%	K ₃ / K ₁ :	1.10
	PGP-2-4	4.00%		

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Example 80

CCP-20CF ₃	4.00%	Clearing point [°C]:	75.0
CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1071
PGU-2-F	2.00%	Δε [1 kHz, 20°C]:	4.1
PGU-3-F	4.00%	γ ₁ [mPa·s, 20°C]:	59
PUQU-2-F	4.00%	V ₁₀ [V]:	1.96
PUQU-3-F	6.00%	V ₅₀ [V]:	2.34
CC-3-V1	13.00%	V ₉₀ [V]:	2.90
CC-4-V	16.00%	V ₉₀ /V ₁₀ :	1.477
CCP-V-1	16.00%	K ₁ [pN]:	11.7
CCG-V-F	9.00%	K ₃ [pN]:	12.6
PCH-301	12.00%	K ₃ / K ₁ :	1.08
PGP-2-3	5.00%		
PGP-2-4	5.00%		

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15Example 81

CCP-1F.F.F	8.00%	Clearing point [°C]:	76.0
CCP-3F.F.F	10.00%	Δn [589 nm, 20°C]:	0.1041
CCP-20CF ₃	10.00%	Δε [1 kHz, 20°C]:	7.9
CCP-30CF ₃	4.00%	γ ₁ [mPa·s, 20°C]:	78
PUQU-2-F	10.00%	V ₁₀ [V]:	1.50
PUQU-3-F	10.00%	V ₅₀ [V]:	1.83
PCH-301	5.00%	V ₉₀ [V]:	2.30
CCP-V-1	10.00%	V ₉₀ /V ₁₀ :	1.530
CCP-V2-1	8.00%	K ₁ [pN]:	12.1
CC-3-V1	12.00%	K ₃ [pN]:	13.5
CC-5-V	5.00%	K ₃ / K ₁ :	1.12
PGP-2-3	4.00%		
PP-1-2V1	4.00%		

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Example 82

5 10 15	CCP-20CF ₃	4.00%	Clearing point [°C]:	80.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1038
	PGU-3-F	5.00%	Δε [1 kHz, 20°C]:	6.0
	PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	69
	PUQU-3-F	10.00%	V ₁₀ [V]:	1.67
	CC-3-V1	13.00%	V ₅₀ [V]:	2.01
	CC-4-V	18.00%	V ₉₀ [V]:	2.51
	CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.503
	CCP-V2-1	5.00%	K ₁ [pN]:	12.1
	CCG-V-F	8.00%	K ₃ [pN]:	13.5
	PCH-301	6.00%	K ₃ / K ₁ :	1.11
	PGP-2-3	5.00%		
	CCGU-3-F	4.00%		

Example 83

20 25 30	CCP-20CF ₃	4.00%	Clearing point [°C]:	78.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1143
	PGU-3-F	3.00%	Δε [1 kHz, 20°C]:	4.9
	PUQU-2-F	7.00%	γ ₁ [mPa·s, 20°C]:	68
	PUQU-3-F	10.00%	V ₁₀ [V]:	1.91
	CC-3-V1	16.00%	V ₅₀ [V]:	2.27
	CC-4-V	10.00%	V ₉₀ [V]:	2.80
	PCH-301	12.00%	V ₉₀ /V ₁₀ :	1.466
	CCP-V-1	12.00%	K ₁ [pN]:	12.9
	CCP-V2-1	10.00%	K ₃ [pN]:	13.5
	PGP-2-3	6.00%	K ₃ / K ₁ :	1.04
	PGP-2-4	6.00%		

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Example 84

CCP-20CF ₃	4.00%	Clearing point [°C]:	77.5
CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1147
PUQU-2-F	6.00%	Δε [1 kHz, 20°C]:	5.0
5 PUQU-3-F	10.00%	γ ₁ [mPa·s, 20°C]:	70
CC-3-V1	14.00%	V ₁₀ [V]:	1.94
CC-4-V	10.00%	V ₅₀ [V]:	2.31
PCH-301	10.00%	V ₉₀ [V]:	2.84
10 CCP-V-1	10.00%	V ₉₀ /V ₁₀ :	1.464
CCP-V2-1	10.00%	K ₁ [pN]:	13.6
CCGU-3-F	6.00%	K ₃ [pN]:	14.4
PP-1-2V1	10.00%	K ₃ / K ₁ :	1.06
PGP-2-4	6.00%		

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Example 85

CCP-20CF ₃	4.00%	Clearing point [°C]:	79.0
CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1049
PGU-3-F	5.00%	Δε [1 kHz, 20°C]:	6.0
PUQU-2-F	8.00%	γ ₁ [mPa·s, 20°C]:	68
PUQU-3-F	10.00%	V ₁₀ [V]:	1.69
CC-3-V1	13.00%	V ₅₀ [V]:	2.03
25 CC-4-V	15.00%	V ₉₀ [V]:	2.53
CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.497
CCP-V2-1	10.00%	K ₁ [pN]:	12.3
CCG-V-F	8.00%	K ₃ [pN]:	13.6
PCH-301	6.00%	K ₃ / K ₁ :	1.10
30 PGP-2-3	5.00%		

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Example 86

GGP-3-CL	9.00%	Clearing point [°C]:	87.5
GGP-5-CL	23.00%	Δn [589 nm, 20°C]:	0.2040
FET-2CL	7.00%	Δε [1 kHz, 20°C]:	6.9
FET-3CL	4.00%	γ ₁ [mPa·s, 20°C]:	179
FET-5CL	7.00%		
PP-1-2V1	13.00%		
CCP-V-1	12.00%		
CC-3-V1	8.00%		
BCH-2F.F	6.00%		
PGP-2-3	2.00%		
PGP-2-4	3.00%		
PGU-3-F	6.00%		

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Example 87

CCZU-3-F	12.00%	Clearing point [°C]:	81.0
PGU-2-F	3.00%	Δn [589 nm, 20°C]:	0.1043
PGU-3-F	4.00%	Δε [1 kHz, 20°C]:	6.6
PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	72
PUQU-3-F	8.00%	V ₁₀ [V]:	1.60
CC-3-V1	13.00%	V ₅₀ [V]:	1.94
CC-4-V	15.00%	V ₉₀ [V]:	2.41
CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.506
CCP-V2-1	8.00%	K ₁ [pN]:	12.2
CCG-V-F	8.00%	K ₃ [pN]:	13.5
PCH-301	6.00%	K ₃ / K ₁ :	1.10
PGP-2-3	5.00%		

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Example 88

5	GGP-3-CL	9.00%	Clearing point [°C]:	87.5
	GGP-5-CL	20.00%	Δn [589 nm, 20°C]:	0.2017
	FET-2CL	9.00%	Δε [1 kHz, 20°C]:	6.5
10	FET-3CL	4.00%	γ ₁ [mPa·s, 20°C]:	172
	FET-5CL	7.00%		
	PP-1-2V1	13.00%		
	CCP-V-1	14.00%		
15	CC-3-V1	10.00%		
	PGP-2-3	3.00%		
	PGP-2-4	3.00%		
	PGU-3-F	8.00%		

Example 89

20	CCQU-2-F	6.00%	Clearing point [°C]:	80.0
	CCQU-3-F	7.00%	Δn [589 nm, 20°C]:	0.0975
	CCP-20CF ₃	4.00%	Δε [1 kHz, 20°C]:	6.7
25	CCP-30CF ₃	4.00%	γ ₁ [mPa·s, 20°C]:	76
	CC-3-V1	14.00%	V ₁₀ [V]:	1.65
	CC-5-V	10.00%	V ₅₀ [V]:	1.99
	PCH-301	7.00%	V ₉₀ [V]:	2.47
30	CCP-V-1	10.00%	V ₉₀ /V ₁₀ :	1.498
	CCP-V2-1	7.00%	K ₁ [pN]:	12.3
	CCG-V-F	8.00%	K ₃ [pN]:	14.0
	PUQU-2-F	8.00%	K ₃ / K ₁ :	1.13
	PUQU-3-F	10.00%		
	PGP-2-4	5.00%		

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Example 90

5	GGP-3-CL	9.00%	Clearing point [°C]: 90.0
	GGP-5-CL	20.00%	Δn [589 nm, 20°C]: 0.1989
	FET-2CL	7.00%	Δε [1 kHz, 20°C]: 7.4
	FET-3CL	3.00%	
	FET-5CL	6.00%	
	PP-1-2V1	14.00%	
	PGP-2-3	3.00%	
	PGP-2-4	3.00%	
	PGU-3-F	7.00%	
	CCG-V-F	9.00%	
10	CCGU-3-F	4.00%	
	CC-3-V1	7.00%	
	CCP-V-1	8.00%	
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Example 91

20	CCP-1F.F.F	6.00%	Clearing point [°C]: 72.0
	CCP-3F.F.F	10.00%	Δn [589 nm, 20°C]: 0.1119
	CCP-20CF ₃	4.00%	Δε [1 kHz, 20°C]: 7.9
	CCP-30CF ₃	4.00%	γ ₁ [mPa·s, 20°C]: 76
	CCP-40CF ₃	4.00%	K ₁ [pN]: 12.4
	CCP-50CF ₃	4.00%	K ₃ [pN]: 12.8
	PUQU-2-F	10.00%	K ₃ / K ₁ : 1.03
	PUQU-3-F	10.00%	
	CCP-V-1	13.00%	
	CC-3-V1	14.00%	
25	PCH-301	8.00%	
	PGP-2-3	6.50%	
	PP-1-2V1	6.50%	
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Example 92

CCGU-3-F	3.00%	Clearing point [°C]:	75.5
CC-3-V1	18.00%	Δn [589 nm, 20°C]:	0.1133
CC-4-V	8.00%	Δε [1 kHz, 20°C]:	5.0
PCH-301	15.00%	γ ₁ [mPa·s, 20°C]:	73
CCP-V-1	12.00%	V ₁₀ [V]:	1.85
CCP-V2-1	12.00%	V ₅₀ [V]:	2.22
PUQU-2-F	10.00%	V ₉₀ [V]:	2.78
PUQU-3-F	10.00%	V ₉₀ /V ₁₀ :	1.504
PGP-2-3	6.00%	K ₁ [pN]:	13.5
PGP-2-4	6.00%	K ₃ [pN]:	15.5
		K ₃ / K ₁ :	1.15

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Example 93

PGU-2-F	5.00%	Clearing point [°C]:	73.5
PGU-3-F	4.00%	Δn [589 nm, 20°C]:	0.1167
CCQU-3-F	7.00%	Δε [1 kHz, 20°C]:	8.7
PUQU-2-F	9.00%	γ ₁ [mPa·s, 20°C]:	76
PUQU-3-F	9.00%	V ₁₀ [V]:	1.34
CC-3-V1	10.00%	V ₅₀ [V]:	1.63
CC-5-V	10.00%	V ₉₀ [V]:	2.02
CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.507
PCH-301	9.00%	K ₁ [pN]:	10.9
PGP-2-3	3.00%	K ₃ [pN]:	12.5
PGP-2-4	5.00%	K ₃ / K ₁ :	1.15
CCGU-3-F	5.00%		
CCG-V-F	12.00%		

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Example 94

PGU-2-F	5.00%	Clearing point [°C]:	74.0
PGU-3-F	4.00%	Δn [589 nm, 20°C]:	0.1154
CCQU-3-F	7.00%	Δε [1 kHz, 20°C]:	8.9
PUQU-2-F	8.00%	γ ₁ [mPa·s, 20°C]:	76
PUQU-3-F	9.00%	V ₁₀ [V]:	1.34
CC-3-V1	11.00%	V ₅₀ [V]:	1.63
CC-5-V	10.00%	V ₉₀ [V]:	2.02
CCP-V-1	11.00%	V ₉₀ /V ₁₀ :	1.507
PCH-301	10.00%	K ₁ [pN]:	11.5
PGP-2-3	3.00%	K ₃ [pN]:	11.9
PGP-2-4	5.00%	K ₃ / K ₁ :	1.03
CCGU-3-F	5.00%		
CCG-V-F	7.00%		
CCZU-3-F	5.00%		

Example 95

CCP-20CF ₃	4.00%	Clearing point [°C]:	75.0
CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1085
PGU-2-F	2.00%	Δε [1 kHz, 20°C]:	4.4
PGU-3-F	4.00%	γ ₁ [mPa·s, 20°C]:	59
PUQU-2-F	5.00%	V ₁₀ [V]:	1.88
PUQU-3-F	6.00%	V ₅₀ [V]:	2.26
CC-3-V1	13.00%	V ₉₀ [V]:	2.81
CC-4-V	16.00%	V ₉₀ /V ₁₀ :	1.495
CCP-V-1	16.00%	K ₁ [pN]:	11.7
CCG-V-F	8.00%	K ₃ [pN]:	12.8
PCH-301	12.00%	K ₃ / K ₁ :	1.10
PGP-2-3	5.00%		
PGP-2-2V	5.00%		

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Example 96

5	CCP-20CF ₃	4.00%	Clearing point [°C]:	80.5
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1057
	PGU-3-F	5.00%	Δε [1 kHz, 20°C]:	6.1
	PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	68
	PUQU-3-F	10.00%	V ₁₀ [V]:	1.69
	CC-3-V1	13.00%	V ₅₀ [V]:	2.04
	CC-4-V	18.00%	V ₉₀ [V]:	2.55
	CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.509
	CCP-V2-1	5.00%	K ₁ [pN]:	12.1
	CCG-V-F	8.00%	K ₃ [pN]:	13.6
10	PCH-301	6.00%	K ₃ / K ₁ :	1.12
	PGP-2-2V	5.00%		
	CCGU-3-F	4.00%		
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Example 97

20	CCP-20CF ₃	4.00%	Clearing point [°C]:	79.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1049
	PGU-3-F	3.00%	Δε [1 kHz, 20°C]:	5.5
	PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	66
	PUQU-3-F	10.00%	V ₁₀ [V]:	1.75
	CC-3-V1	13.00%	V ₅₀ [V]:	2.11
	CC-4-V	18.00%	V ₉₀ [V]:	2.63
	CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.503
	CCP-V2-1	5.00%	K ₁ [pN]:	12.1
	CCG-V-F	8.00%	K ₃ [pN]:	13.3
25	PCH-301	7.00%	K ₃ / K ₁ :	1.09
	PGP-2-3	5.00%		
	PGP-2-4	2.00%		
	CCGU-3-F	3.00%		
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Example 98

CCZU-3-F	12.00%	Clearing point [°C]:	79.0
PGU-3-F	4.00%	Δn [589 nm, 20°C]:	0.0999
PUQU-2-F	6.00%	Δε [1 kHz, 20°C]:	5.9
PUQU-3-F	8.00%	γ ₁ [mPa·s, 20°C]:	69
CC-3-V1	13.00%	V ₁₀ [V]:	1.66
CC-4-V	16.00%	V ₅₀ [V]:	2.00
CCP-V-1	12.00%	V ₉₀ [V]:	2.48
CCP-V2-1	8.00%	V ₉₀ /V ₁₀ :	1.494
CCG-V-F	8.00%	K ₁ [pN]:	12.0
PCH-301	8.00%	K ₃ [pN]:	13.6
PGP-2-3	5.00%	K ₃ / K ₁ :	1.13

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Example 99

CCP-20CF ₃	4.00%	Clearing point [°C]:	79.0
CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.0980
PUQU-2-F	7.00%	Δε [1 kHz, 20°C]:	5.3
PUQU-3-F	10.00%	γ ₁ [mPa·s, 20°C]:	66
CC-3-V1	13.00%	V ₁₀ [V]:	1.79
CC-4-V	18.00%	V ₅₀ [V]:	2.15
CCP-V-1	12.00%	V ₉₀ [V]:	2.68
CCP-V2-1	5.00%	V ₉₀ /V ₁₀ :	1.497
CCG-V-F	10.00%	K ₁ [pN]:	11.8
PCH-301	8.00%	K ₃ [pN]:	13.8
PGP-2-3	5.00%	K ₃ / K ₁ :	1.17
CCGU-3-F	4.00%		

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Example 100

CCP-20CF ₃	4.50%	Clearing point [°C]:	79.5
CCP-30CF ₃	4.50%	Δn [589 nm, 20°C]:	0.1033
CCZU-3-F	5.00%	Δε [1 kHz, 20°C]:	5.2
PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	66
PUQU-3-F	10.00%	V ₁₀ [V]:	1.76
CC-3-V1	13.00%	V ₅₀ [V]:	2.12
CC-4-V	15.00%	V ₉₀ [V]:	2.62
CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.489
CCP-V2-1	5.00%	K ₁ [pN]:	12.3
CCG-V-F	8.00%	K ₃ [pN]:	13.4
PCH-301	8.00%	K ₃ / K ₁ :	1.08
PGP-2-3	5.00%		
PGP-2-4	4.00%		

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Example 101

CC-3-V1	10.00%	Clearing point [°C]:	77.5
CC-4-V	14.00%	Δn [589 nm, 20°C]:	0.0934
PGP-2-3	4.00%	Δε [1 kHz, 20°C]:	8.7
PGP-2-4	4.00%	γ ₁ [mPa·s, 20°C]:	83
CCG-V-F	10.00%	V ₁₀ [V]:	1.38
PUQU-2-F	8.00%	V ₅₀ [V]:	1.68
PUQU-3-F	7.00%	V ₉₀ [V]:	2.09
CCQU-2-F	7.00%	V ₉₀ /V ₁₀ :	1.516
CCQU-3-F	12.00%		
CCQU-5-F	10.00%		
CCP-3F.F.F	3.00%		
CCP-20CF ₃	5.00%		
CCP-30CF ₃	6.00%		

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Example 102

5	CCP-2F.F.F	8.00%	Clearing point [°C]:	81.0
	CCP-3F.F.F	6.00%	Δn [589 nm, 20°C]:	0.0808
	CCQU-2-F	11.00%	Δε [1 kHz, 20°C]:	16.5
	CCQU-3-F	12.00%	γ ₁ [mPa·s, 20°C]:	164
	CCQU-5-F	10.00%	V ₁₀ [V]:	0.95
	ACQU-2-F	8.00%	V ₅₀ [V]:	1.20
	ACQU-3-F	10.00%	V ₉₀ [V]:	1.50
	ACQU-4-F	10.00%	V ₉₀ /V ₁₀ :	1.587
	AUUQGU-3-F	9.00%		
	CC-4-V	12.00%		
	PGP-2-4	4.00%		

15 Example 103

20	PCH-301	6.00%	Clearing point [°C]:	76.0
	CC-4-V	14.00%	Δn [589 nm, 20°C]:	0.0927
	CCP-V-1	10.00%	Δε [1 kHz, 20°C]:	8.7
	CCG-V-F	13.00%	γ ₁ [mPa·s, 20°C]:	90
	PUQU-2-F	8.00%	V ₁₀ [V]:	1.32
	PUQU-3-F	7.00%	V ₅₀ [V]:	1.62
	CCQU-3-F	8.00%	V ₉₀ [V]:	2.02
	CCQU-5-F	7.00%	V ₉₀ /V ₁₀ :	1.527
	ACQU-2-F	6.00%		
	ACQU-3-F	6.00%		
25	CCP-30CF ₃	6.00%		
	CCP-40CF ₃	4.00%		
	PGP-2-4	3.00%		
	PGP-2-3	2.00%		
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Example 104

CC-4-V	15.00%	Clearing point [°C]:	86.0
CC-3-V1	2.00%	Δn [589 nm, 20°C]:	0.0900
CCQU-2-F	13.00%	$\Delta \epsilon$ [1 kHz, 20°C]:	11.2
CCQU-3-F	13.00%	γ_1 [mPa·s, 20°C]:	109
CCQU-5-F	12.00%	V_{10} [V]:	1.28
CCP-20CF ₃	8.00%	V_{50} [V]:	1.58
CCP-30CF ₃	8.00%	V_{90} [V]:	1.98
CCP-50CF ₃	5.00%	V_{90}/V_{10} :	1.549
PUQU-2-F	7.00%		
PUQU-3-F	9.00%		
PGP-2-3	3.00%		
CCGU-3-F	5.00%		

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Example 105

CC-3-V1	11.00%	Clearing point [°C]:	80.0
CC-4-V	14.00%	Δn [589 nm, 20°C]:	0.0938
PGP-2-3	4.00%	$\Delta \epsilon$ [1 kHz, 20°C]:	8.7
PGP-2-4	4.00%	γ_1 [mPa·s, 20°C]:	86
CCG-V-F	9.00%	V_{10} [V]:	1.41
PUQU-2-F	8.00%	V_{50} [V]:	1.72
PUQU-3-F	7.00%	V_{90} [V]:	2.14
CCQU-2-F	7.00%	V_{90}/V_{10} :	1.514
CCQU-3-F	13.00%		
CCQU-5-F	12.00%		
CCP-30CF ₃	5.00%		
CCP-40CF ₃	6.00%		

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Example 106

ECCP-3F.F	7.00%	Clearing point [°C]:	78.5
CCP-20CF ₃	4.50%	Δn [589 nm, 20°C]:	0.1008
CCP-30CF ₃	4.50%	Δε [1 kHz, 20°C]:	4.5
PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	70
PUQU-3-F	10.00%	V ₁₀ [V]:	2.00
CC-4-V	10.00%	V ₅₀ [V]:	2.40
CC-3-V1	14.00%	V ₉₀ [V]:	3.01
CCP-V-1	15.00%	V ₉₀ /V ₁₀ :	1.503
CCP-V2-1	8.00%	K ₁ [pN]:	12.6
PCH-301	15.00%	K ₃ [pN]:	14.7
PGP-2-3	6.00%	K ₃ / K ₁ :	1.16

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Example 107

CCZU-3-F	13.00%	Clearing point [°C]:	81.5
PGU-2-F	2.00%	Δn [589 nm, 20°C]:	0.1039
PGU-3-F	4.00%	Δε [1 kHz, 20°C]:	6.7
PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	73
PUQU-3-F	10.00%	V ₁₀ [V]:	1.62
CC-3-V1	13.00%	V ₅₀ [V]:	1.97
CC-4-V	15.00%	V ₉₀ [V]:	2.45
CCP-V-1	12.00%	V ₉₀ /V ₁₀ :	1.512
CCP-V2-1	8.00%	K ₁ [pN]:	12.6
CCG-V-F	7.00%	K ₃ [pN]:	13.7
PCH-301	5.00%	K ₃ / K ₁ :	1.09
PGP-2-3	5.00%		

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Example 108

5	CC-4-V	18.00%	Clearing point [°C]:	79.0
	CCP-V-1	10.00%	Δn [589 nm, 20°C]:	0.0931
	CCG-V-F	14.00%	Δε [1 kHz, 20°C]:	8.9
	PUQU-2-F	8.00%	γ ₁ [mPa·s, 20°C]:	88
	PUQU-3-F	7.00%	V ₁₀ [V]:	1.33
	CCQU-2-F	3.00%	V ₅₀ [V]:	1.63
	CCQU-3-F	5.00%	V ₉₀ [V]:	2.03
	CCQU-5-F	6.00%	V ₉₀ /V ₁₀ :	1.532
10	ACQU-2-F	7.00%		
	ACQU-3-F	6.00%		
	CCP-30CF ₃	6.00%		
	CCP-40CF ₃	4.00%		
15	PGP-2-4	3.00%		
	PGP-2-3	3.00%		

Example 109

20	CCP-20CF ₃	4.00%	Clearing point [°C]:	77.0
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1131
	PGU-2-F	2.00%	Δε [1 kHz, 20°C]:	4.7
	PGU-3-F	4.00%	K ₁ [pN]:	12.3
	PUQU-2-F	6.00%	K ₃ [pN]:	13.3
	PUQU-3-F	8.00%	K ₃ / K ₁ :	1.08
	CC-3-V1	14.00%		
	CC-4-V	10.00%		
	PCH-301	15.00%		
	CCP-V-1	14.00%		
25	CCP-V2-1	9.00%		
	PGP-2-3	5.00%		
	PGP-2-4	5.00%		
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Example 110

5	PGU-2-F	3.00%	Clearing point [°C]:	79.5
	CC-5-V	15.00%	Δn [589 nm, 20°C]:	0.1206
	CC-3-V1	11.00%	Δε [1 kHz, 20°C]:	6.6
	PCH-301	11.00%	γ ₁ [mPa·s, 20°C]:	80
	CCP-V-1	11.00%	V ₁₀ [V]:	1.60
	CCP-V2-1	9.00%	V ₅₀ [V]:	1.95
	GGP-3-CL	5.00%	V ₉₀ [V]:	2.43
	PUQU-2-F	9.00%	V ₉₀ /V ₁₀ :	1.519
	PUQU-3-F	9.00%	K ₁ [pN]:	12.6
	PGP-2-3	3.00%	K ₃ [pN]:	13.7
10	PGP-2-4	6.00%	K ₃ / K ₁ :	1.09
	CCGU-3-F	6.00%		
	CCQU-2-F	2.00%		
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Example 111

20	CCZU-3-F	14.00%	Clearing point [°C]:	80.0
	PGU-2-F	2.00%	Δn [589 nm, 20°C]:	0.1050
	PGU-3-F	5.00%	Δε [1 kHz, 20°C]:	7.6
	PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	74
	PUQU-3-F	10.00%	V ₁₀ [V]:	1.51
	CC-3-V1	13.00%	V ₅₀ [V]:	1.82
	CC-4-V	15.00%	V ₉₀ [V]:	2.26
	CCP-V-1	10.00%	V ₉₀ /V ₁₀ :	1.502
	CCP-V2-1	8.00%	K ₁ [pN]:	12.1
	CCG-V-F	8.00%	K ₃ [pN]:	13.2
25	PCH-301	4.00%	K ₃ / K ₁ :	1.09
	PGP-2-3	5.00%		
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Example 112

5	PGU-3-F	2.00%	Clearing point [°C]:	80.5
	CCP-2F.F.F	6.00%	Δn [589 nm, 20°C]:	0.0974
	CCP-3F.F.F	12.00%	Δε [1 kHz, 20°C]:	7.0
	CCP-20CF ₃	4.00%	γ ₁ [mPa·s, 20°C]:	73
	CCP-30CF ₃	4.00%	V ₁₀ [V]:	1.61
	CC-3-V1	16.00%	V ₅₀ [V]:	1.95
	CC-4-V	14.00%	V ₉₀ [V]:	2.43
	PCH-301	2.00%	V ₉₀ /V ₁₀ :	1.511
	CCP-V-1	8.00%	K ₁ [pN]:	12.5
	CCP-V2-1	10.00%	K ₃ [pN]:	13.8
10	PUQU-2-F	7.00%	K ₃ / K ₁ :	1.10
	PUQU-3-F	10.00%		
	PGP-2-4	5.00%		
15				

Example 113

20	CCP-20CF ₃	4.00%	Clearing point [°C]:	79.5
	CCP-30CF ₃	4.00%	Δn [589 nm, 20°C]:	0.1130
	PGU-3-F	3.00%	Δε [1 kHz, 20°C]:	5.3
	PUQU-2-F	6.00%	γ ₁ [mPa·s, 20°C]:	72
	PUQU-3-F	10.00%	V ₁₀ [V]:	1.82
	CC-3-V1	15.00%	V ₅₀ [V]:	2.18
	CC-4-V	9.00%	V ₉₀ [V]:	2.69
	PCH-301	15.00%	V ₉₀ /V ₁₀ :	1.482
	CCP-V-1	11.00%	K ₁ [pN]:	12.5
	CCP-V2-1	9.00%	K ₃ [pN]:	13.7
25	CCGU-3-F	4.00%	K ₃ / K ₁ :	1.09
	PGP-2-3	5.00%		
	PGP-2-4	5.00%		
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Example 114

5 10 15	CCQU-2-F	4.00%	Clearing point [°C]:	78.5
	CCQU-3-F	9.00%	Δn [589 nm, 20°C]:	0.0970
	CCP-20CF ₃	4.00%	Δε [1 kHz, 20°C]:	6.6
	CCP-30CF ₃	4.00%	γ ₁ [mPa·s, 20°C]:	70
	CC-3-V1	12.00%	V ₁₀ [V]:	1.59
	CC-4-V	12.00%	V ₅₀ [V]:	1.94
	PCH-301	7.00%	V ₉₀ [V]:	2.42
	CCP-V-1	11.00%	V ₉₀ /V ₁₀ :	1.527
	CCP-V2-1	6.00%	K ₁ [pN]:	11.9
	CCG-V-F	8.00%	K ₃ [pN]:	13.5
20 25 30	PUQU-2-F	8.00%	K ₃ / K ₁ :	1.13
	PUQU-3-F	10.00%		
	PGP-2-3	5.00%		

Example 115

20 25 30	CCQU-2-F	6.00%	Clearing point [°C]:	80.0
	CCQU-3-F	10.00%	Δn [589 nm, 20°C]:	0.0981
	CCP-20CF ₃	4.00%	Δε [1 kHz, 20°C]:	7.1
	CCP-30CF ₃	4.00%	γ ₁ [mPa·s, 20°C]:	75
	CC-3-V1	12.00%	V ₁₀ [V]:	1.58
	CC-4-V	9.00%	V ₅₀ [V]:	1.91
	PCH-301	7.00%	V ₉₀ [V]:	2.36
	CCP-V-1	11.00%	V ₉₀ /V ₁₀ :	1.495
	CCP-V2-1	6.00%	K ₁ [pN]:	11.9
	CCG-V-F	8.00%	K ₃ [pN]:	13.7
20 25 30	PUQU-2-F	8.00%	K ₃ / K ₁ :	1.16
	PUQU-3-F	10.00%		
	PGP-2-3	5.00%		

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Example 116

5	CCP-1F.F.F	8.00%	Clearing point [°C]:	73.5
	CCP-3F.F.F	10.00%	Δn [589 nm, 20°C]:	0.1038
	CCP-20CF ₃	9.00%	$\Delta \epsilon$ [1 kHz, 20°C]:	7.9
	CCP-30CF ₃	5.00%	γ_1 [mPa·s, 20°C]:	76
	PUQU-2-F	10.00%	V ₁₀ [V]:	1.49
	PUQU-3-F	10.00%	V ₅₀ [V]:	1.80
	PCH-301	5.00%	V ₉₀ [V]:	2.23
	CCP-V-1	10.00%	V ₉₀ /V ₁₀ :	1.502
	CCP-V2-1	6.00%	K ₁ [pN]:	12.2
	CC-3-V1	12.00%	K ₃ [pN]:	13.0
10	CC-5-V	6.00%	K ₃ / K ₁ :	1.07
	PGP-2-3	4.50%		
	PP-1-2V1	4.50%		
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Example 117

20	CCP-1F.F.F	9.00%	Clearing point [°C]:	74.5
	CCP-3F.F.F	9.00%	Δn [589 nm, 20°C]:	0.1040
	CCP-20CF ₃	9.00%	$\Delta \epsilon$ [1 kHz, 20°C]:	7.9
	CCP-30CF ₃	4.00%	γ_1 [mPa·s, 20°C]:	73
	PUQU-2-F	10.00%	V ₁₀ [V]:	1.50
	PUQU-3-F	10.00%	V ₅₀ [V]:	2.33
	CCP-V-1	10.00%	V ₉₀ [V]:	2.26
	CCP-V2-1	5.00%	V ₉₀ /V ₁₀ :	1.506
	CC-3-V1	13.00%	K ₁ [pN]:	12.8
	CC-5-V	11.00%	K ₃ [pN]:	13.1
25	PGP-2-3	5.00%	K ₃ / K ₁ :	1.02
	PP-1-2V1	5.00%		
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Example 118

5	CCP-1F.F.F	8.00%	Clearing point [°C]:	74.0
	CCP-3F.F.F	10.00%	Δn [589 nm, 20°C]:	0.1055
	CCP-20CF ₃	9.00%	Δε [1 kHz, 20°C]:	7.9
	CCP-30CF ₃	8.00%	γ ₁ [mPa·s, 20°C]:	72
	PUQU-2-F	10.00%	V ₁₀ [V]:	1.52
	PUQU-3-F	9.00%	V ₅₀ [V]:	1.84
	CCP-V-1	5.00%	V ₉₀ [V]:	2.27
	CCP-V2-1	5.00%	V ₉₀ /V ₁₀ :	1.490
	CC-3-V1	13.00%	K ₁ [pN]:	13.2
	CC-5-V	11.00%	K ₃ [pN]:	12.9
10	PGP-2-3	6.00%	K ₃ / K ₁ :	0.98
	PP-1-2V1	6.00%		

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Example 119

20	CCP-1F.F.F	8.00%	Clearing point [°C]:	73.5
	CCP-3F.F.F	10.00%	Δn [589 nm, 20°C]:	0.1056
	CCP-20CF ₃	10.00%	Δε [1 kHz, 20°C]:	7.8
	CCP-30CF ₃	10.00%	γ ₁ [mPa·s, 20°C]:	72
	PUQU-2-F	10.00%	V ₁₀ [V]:	1.50
	PUQU-3-F	8.00%	V ₅₀ [V]:	1.83
	CCP-V-1	4.00%	V ₉₀ [V]:	2.25
	CCP-V2-1	3.00%	V ₉₀ /V ₁₀ :	1.497
	CC-3-V1	12.00%	K ₁ [pN]:	13.4
	CC-5-V	12.00%	K ₃ [pN]:	12.7
25	PGP-2-3	6.50%	K ₃ / K ₁ :	0.95
	PP-1-2V1	6.50%		
30				

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